

Detector R&D for a CLIC Vertex Detector

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University of Liverpool
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on behalf of the
CLIC detector and physics study



Outline



- CLIC physics and accelerator
- Vertex-detector requirements
- Detector optimization studies
- R&D on sensors and readout
- Powering, cooling and detector integration
- Summary / Conclusions

CLIC detector & physics study



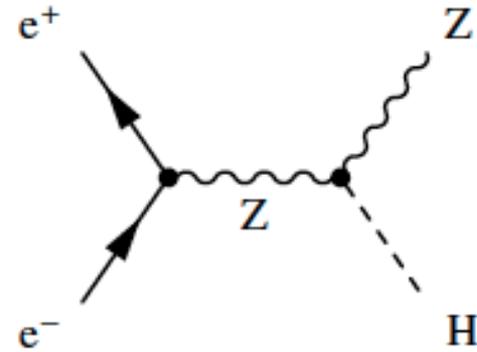
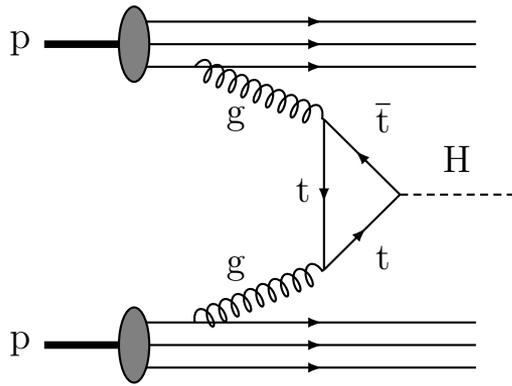
CLICdp member institutes

- Dept. of Physics, Aarhus University
- Laboratoire d'Annecy-le-Vieux de Physique des Particules (LAPP), Annecy
- Vinca Institute for Nuclear Sciences, Belgrade
- University of Bergen
- The School of Physics and Astronomy, University of Birmingham
- Institute of Space Science, Bucharest
- Dept. of Physics, University of Cambridge
- Dept. of Physics and Technology, AGH University of Science and Technology, Cracow
- Polish Academy of Sciences, Cracow
- CERN, Geneva
- University of Glasgow
- Argonne National Laboratory, Lemont
- Australian Collaboration for Accelerator Science (ACAS), Melbourne
- University of Michigan, Ann Arbor
- NC PHEP, Belarusian State University, Minsk
- MPI Munich
- Dept. of Physics, Oxford University
- Institute of Physics of the Academy of Sciences of the Czech Republic, Prague
- Pontificia Universidad Católica de Chile, Santiago de Chile
- Spanish Network for Future Linear Colliders
- Dept. of Physics, Tel Aviv University



- Pre-collaboration structure based on “Memorandum of Cooperation”:
<http://lcd.web.cern.ch/lcd/Home/MoC.html>
- CERN acts as host laboratory
- Currently 21 institutes from 16 countries, more contributors most welcome!
- The CLIC accelerator R&D is being conducted in collaboration with ~48 institutes

Hadron vs. lepton colliders

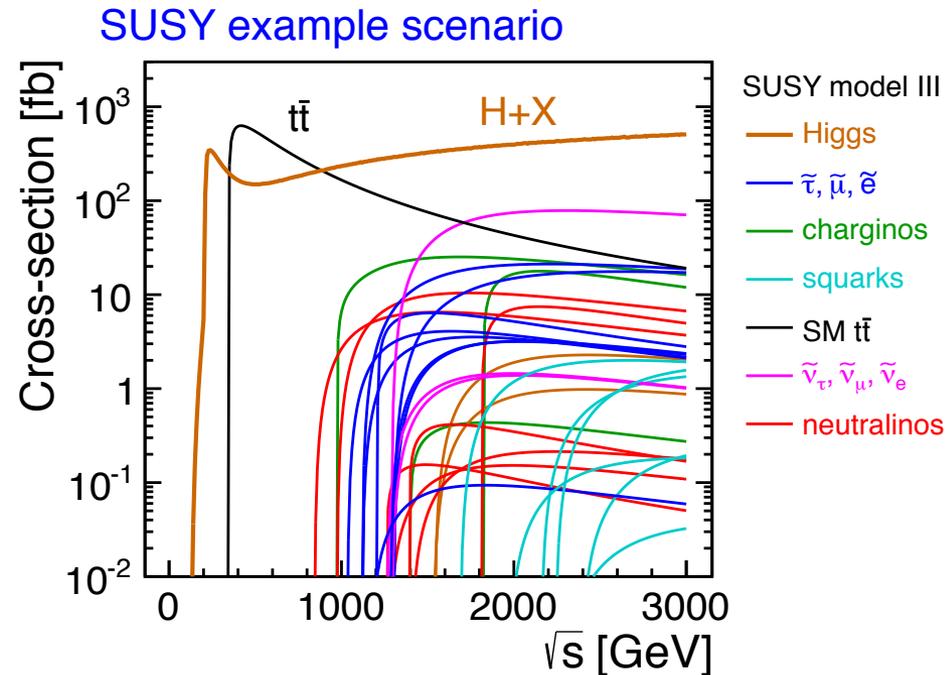
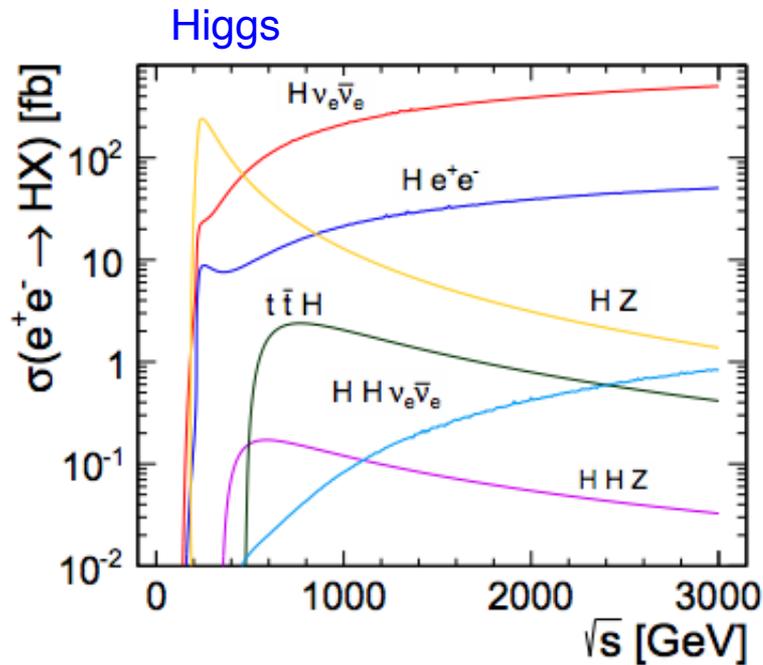


p-p collisions	e ⁺ e ⁻ collisions
<p>Proton is compound object</p> <ul style="list-style-type: none"> → Initial state not known event-by-event → Limits achievable precision 	<p>e⁺/e⁻ are point-like</p> <ul style="list-style-type: none"> → Initial state well defined (\sqrt{s} / polarization) → High-precision measurements
<p>Circular colliders feasible</p>	<p>Linear Colliders (avoid synchrotron rad.)</p>
<p>High rates of QCD backgrounds</p> <ul style="list-style-type: none"> → Complex triggering schemes → High levels of radiation 	<p>Cleaner experimental environment</p> <ul style="list-style-type: none"> → trigger-less readout → Low radiation levels
<p>\sqrt{s} constrained by design</p>	<p>\sqrt{s} can be tuned</p> <ul style="list-style-type: none"> → Threshold scans
<p>High cross-sections for colored-states</p>	<p>Superior sensitivity for electro-weak states</p>

CLIC physics program

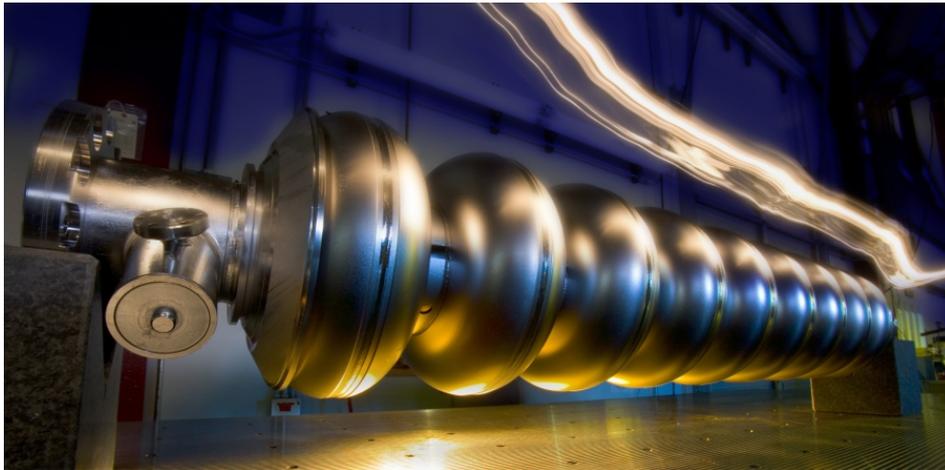


- CLIC: linear e^+e^- collider concept, \sqrt{s} from few hundred GeV up to 3 TeV
- Physics goals:
 - Precision measurements of SM processes (Higgs, top)
 - Precision measurements of new physics potentially discovered at 14 TeV LHC
 - Search for new physics: unique sensitivity to particles with electroweak charge



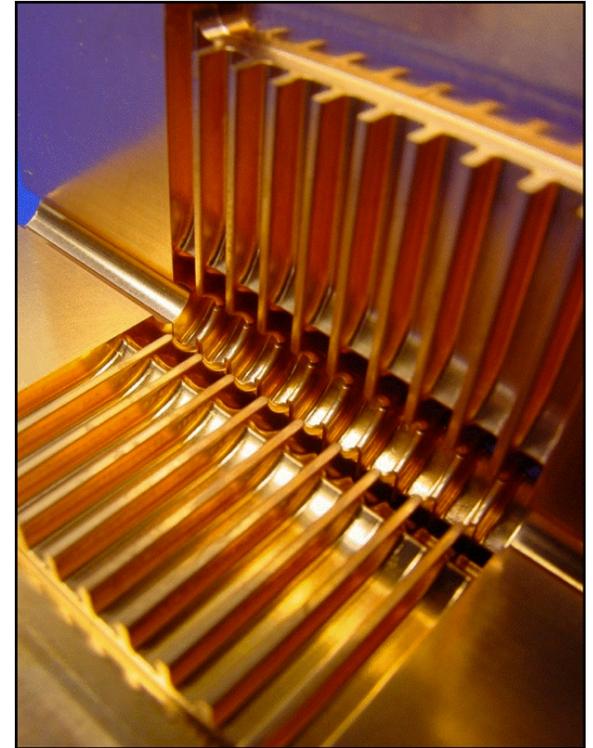
- Linear e^+e^- colliders
- Luminosities: few $10^{34} \text{ cm}^{-2}\text{s}^{-1}$

ILC



- superconducting RF cavities (like XFEL)
- Gradient 32 MV/m
- $\sqrt{s} \leq 500 \text{ GeV}$ (1 TeV upgrade option)
- Focus on $\leq 500 \text{ GeV}$, ongoing studies for 1 TeV

CLIC

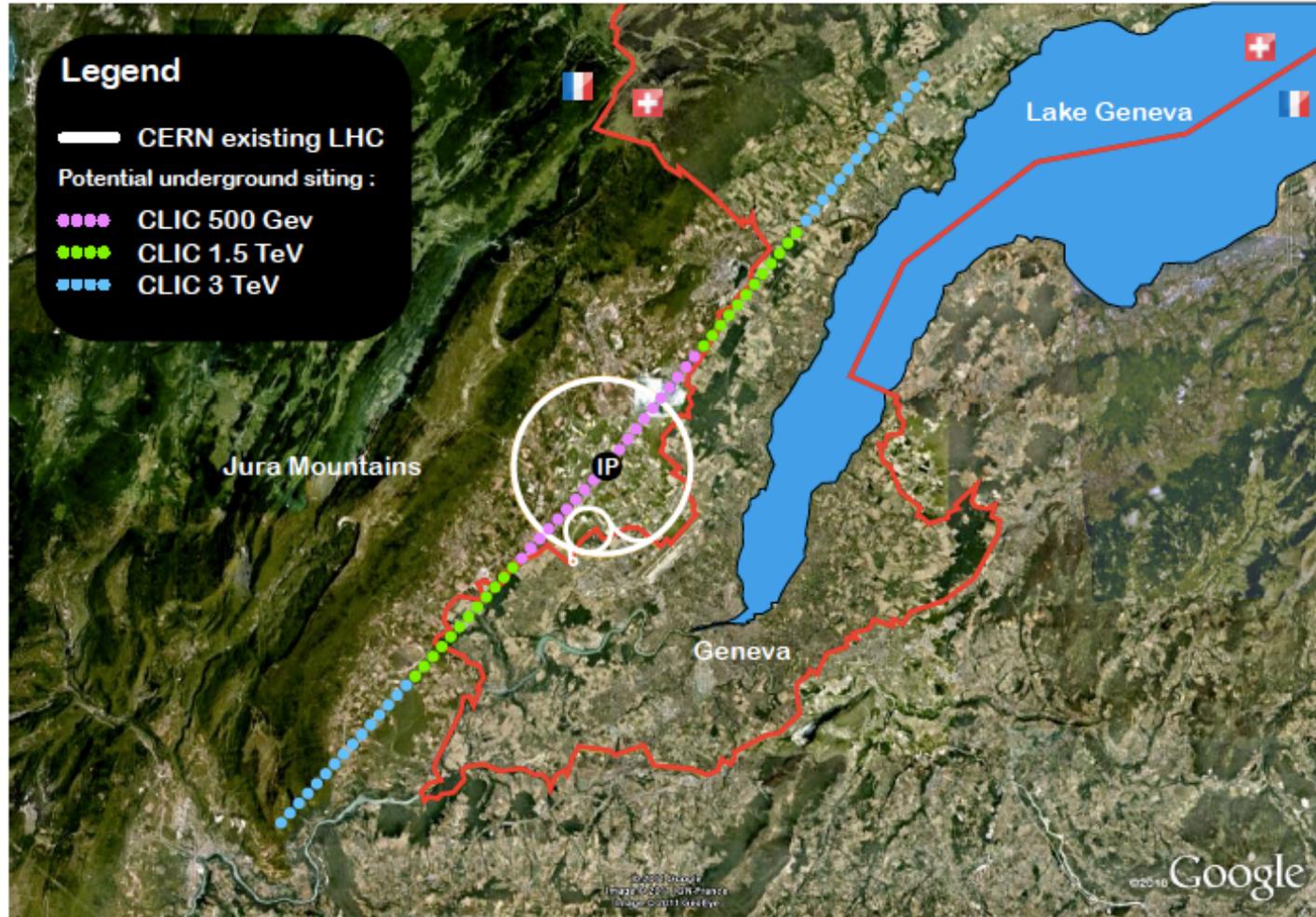


- 2-beam acceleration scheme operated at room temperature
- Gradient 100 MV/m
- \sqrt{s} up to 3 TeV
- Physics + Detector studies for 350 GeV - 3 TeV

CLIC implementation



- Example of staged CLIC implementation underground near CERN
- ~48 km tunnel length for 3 TeV stage
- The site specifications do not constrain the implementation to this location



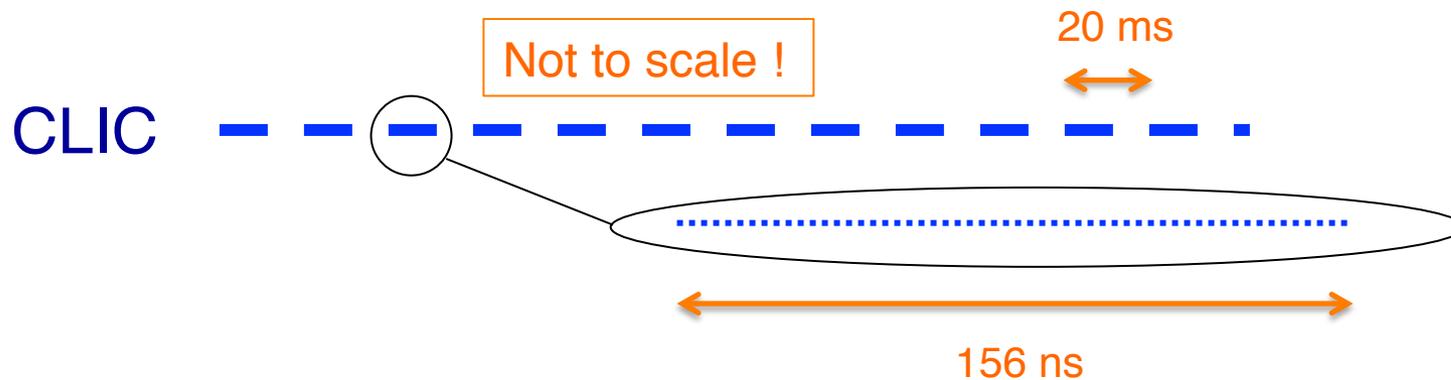
Machine parameters



	LHC at 14 TeV	ILC at 500 GeV	CLIC at 3 TeV
L ($\text{cm}^{-2}\text{s}^{-1}$)	1×10^{34}	2×10^{34}	6×10^{34}
BX separation	25 ns	554 ns	0.5 ns
#BX / train	2808	1312	312
Train duration	70 μs	727 μs	156 ns
Train repetition	14 kHz	5 Hz	50 Hz
Duty cycle	~ 1	0.36%	0.00078%
σ_x / σ_y [nm]	15000 / 15000	474 / 6	$\approx 45 / 1$
σ_z [μm]	~ 50000	300	44

drives timing requirements for detectors

very small beam sizes at interaction point



Beam-induced backgrounds

small beam profiles at IP

→ very high E-fields

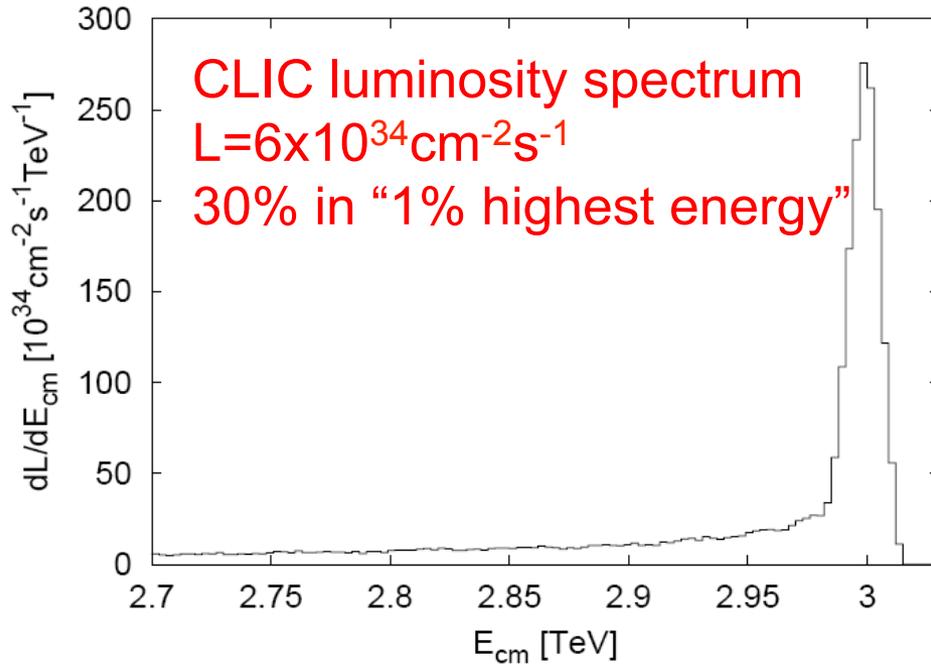
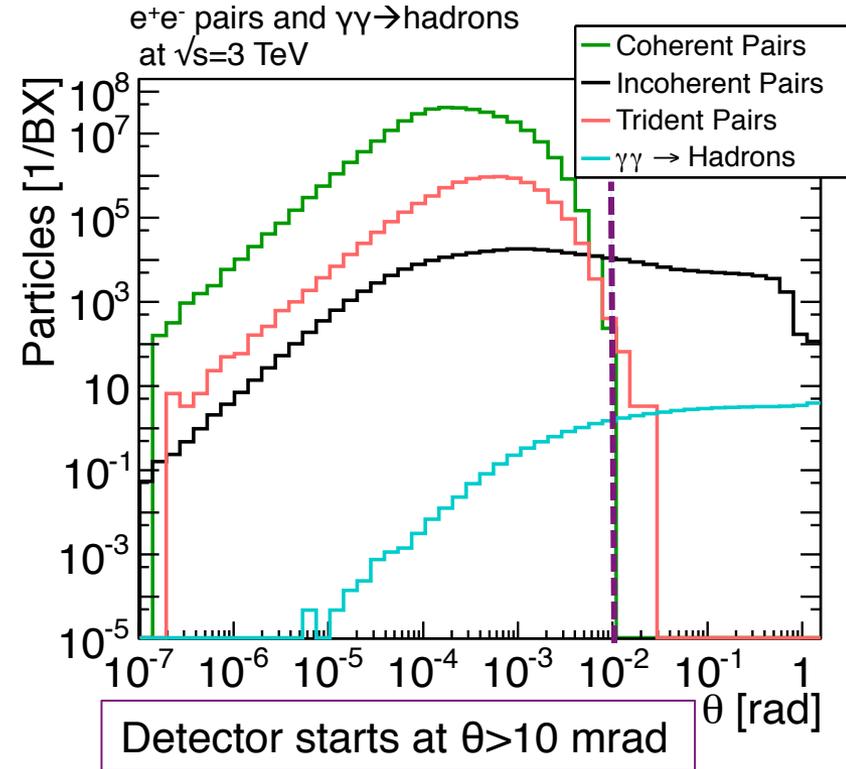
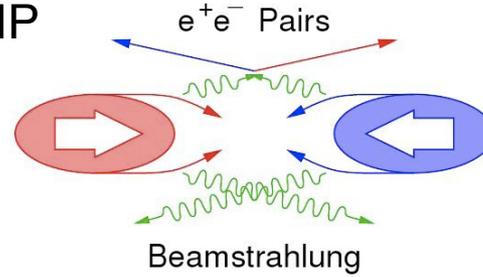
Beamstrahlung

leads to:

- e^+e^- pairs
- hadronic events

→ Reduces E_{cm}

→ Background particles



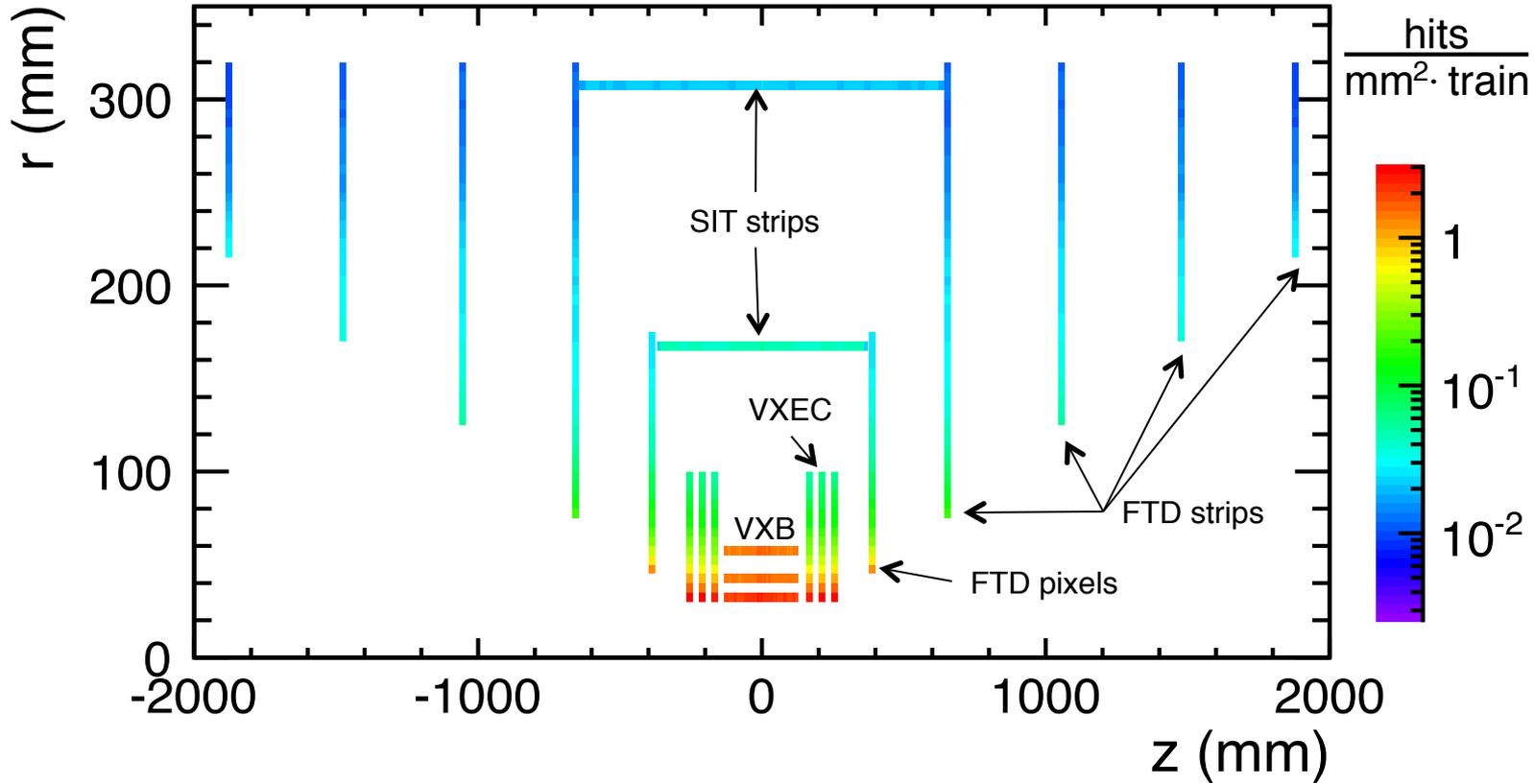
Main backgrounds in detector:

- **Incoherent e^+e^- pairs**: 60 particles / BX
 detector design issue (occupancies)
- **$\gamma\gamma \rightarrow$ hadrons**: 54 particles / BX
 impacts physics

→ Need **pile-up rejection**

Backgrounds in inner tracking region

CLIC_ILD incoherent pairs + $\gamma\gamma \rightarrow$ hadrons: silicon hits, no safety factors



- Train occupancies **up to 3%** in vertex region (including clustering and safety factors)
- moderate radiation exposure, **$\sim 10^4$ below LHC**

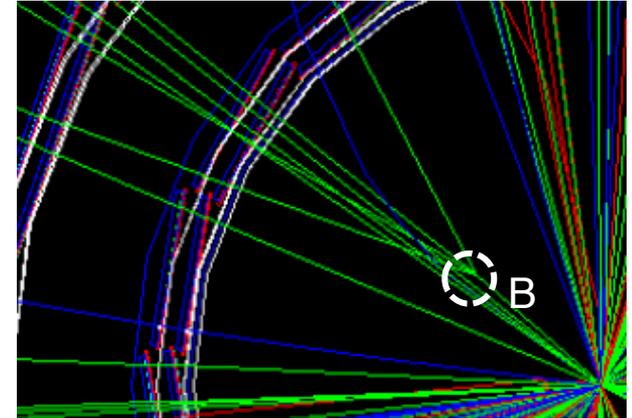
Region	Readout granularity	Max. occup.	NIEL [$n_{eq}/cm^2/y$]	TID [Gy/y]
VXB	20 μm x 20 μm	1.9 %	4×10^{10}	200
VXE	20 μm x 20 μm	2.8 %	5×10^{10}	180
FTD pixels	20 μm x 20 μm	0.6%	2.5×10^{10}	50
FTD strips	10 cm x 50 μm	290 %	1×10^{10}	7
SIT	9 cm x 50 μm	170 %	2×10^9	2

Vertex-detector requirements

- Efficient tagging of heavy quarks through precise determination of displaced vertices:

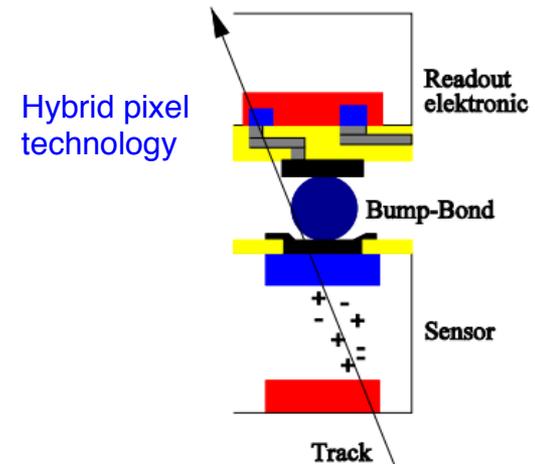
$$\sigma(d_0) = \sqrt{a^2 + b^2} \cdot \text{GeV}^2 / (p^2 \sin^3 \theta)$$

$a \sim 5 \mu\text{m}, b \sim 15 \mu\text{m}$



- good single point resolution: $\sigma_{\text{SP}} \sim 3 \mu\text{m}$
 - small pixels $\sim 25 \times 25 \mu\text{m}^2$, analog readout
- low material budget: $X \lesssim 0.2\% X_0 / \text{layer}$
 - corresponds to $\sim 200 \mu\text{m}$ Si, including supports, cables, cooling
 - low-power ASICs ($\sim 50 \text{ mW/cm}^2$) + gas-flow cooling

- Time slicing with $\sim 10 \text{ ns}$ accuracy, to suppress beam-induced backgrounds
 - High-resistivity sensors, fast readout
 - Hybrid concept (like for LHC detectors):
 - ultra-thin sensors
 - + high-performance r/o ASICs

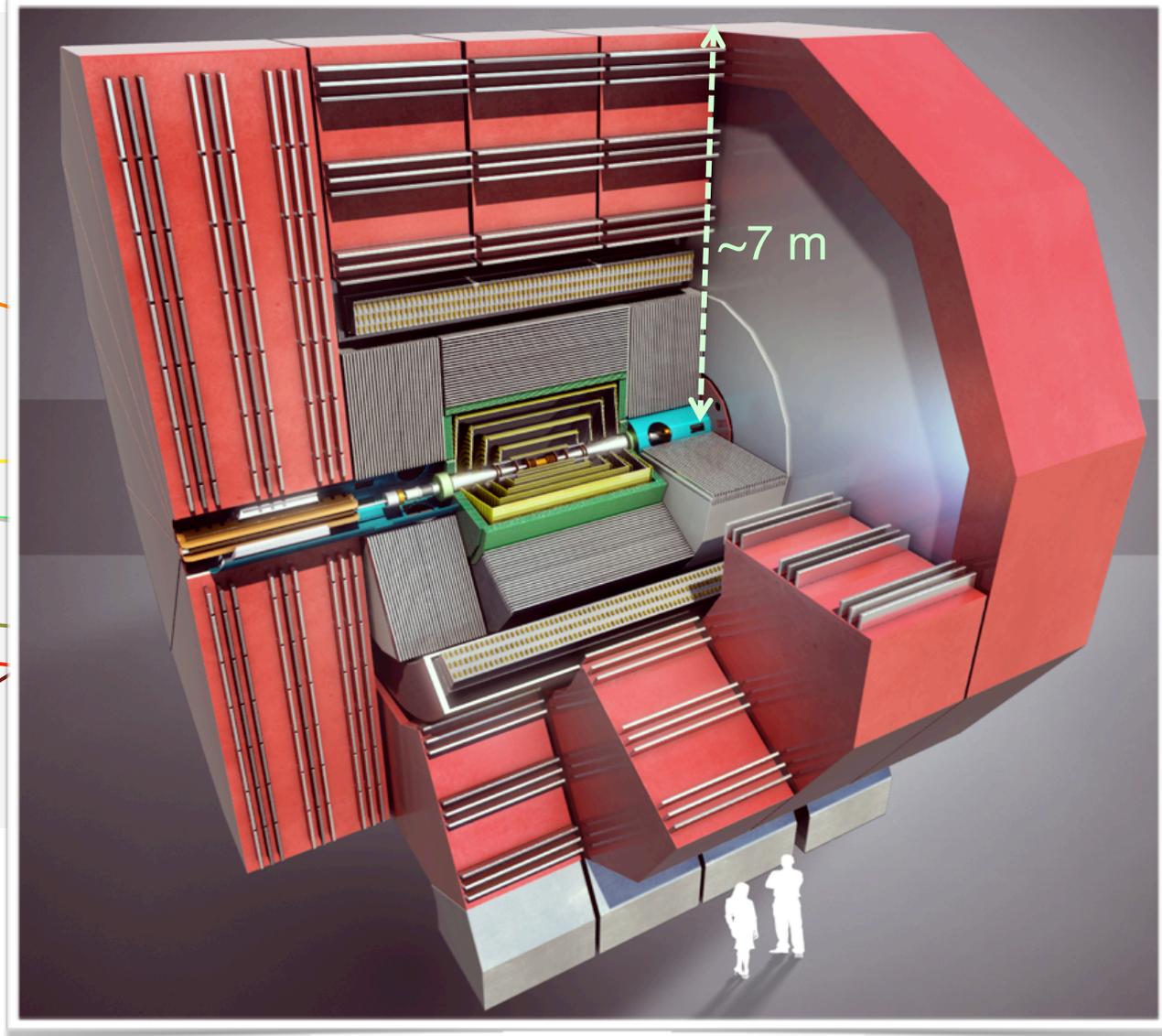


CLIC detector concepts



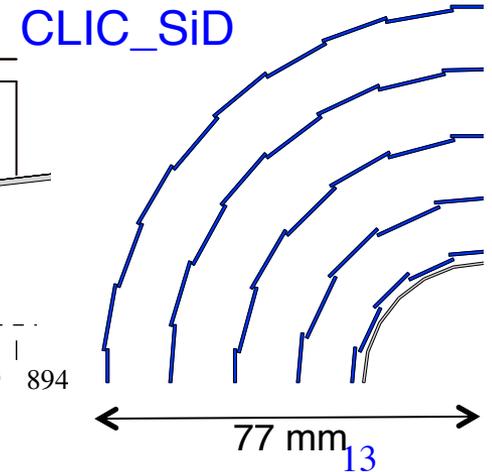
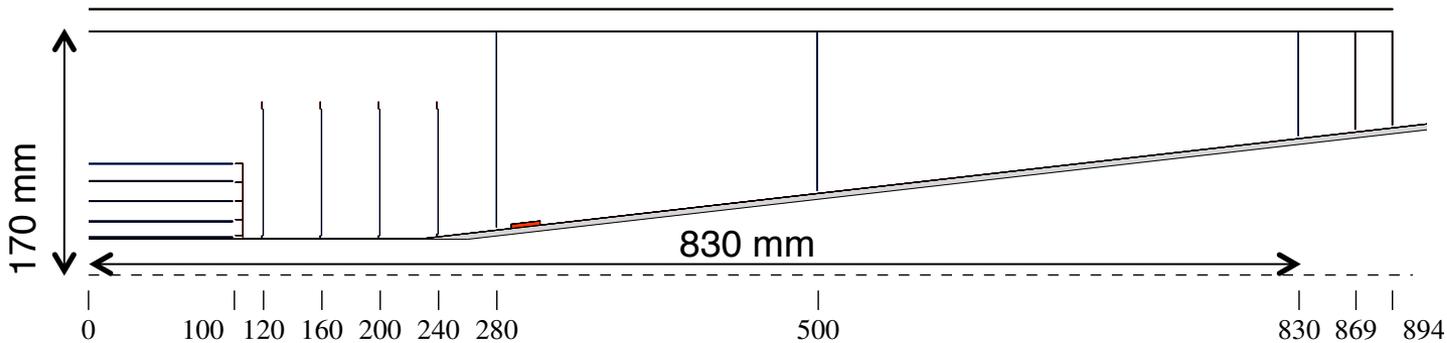
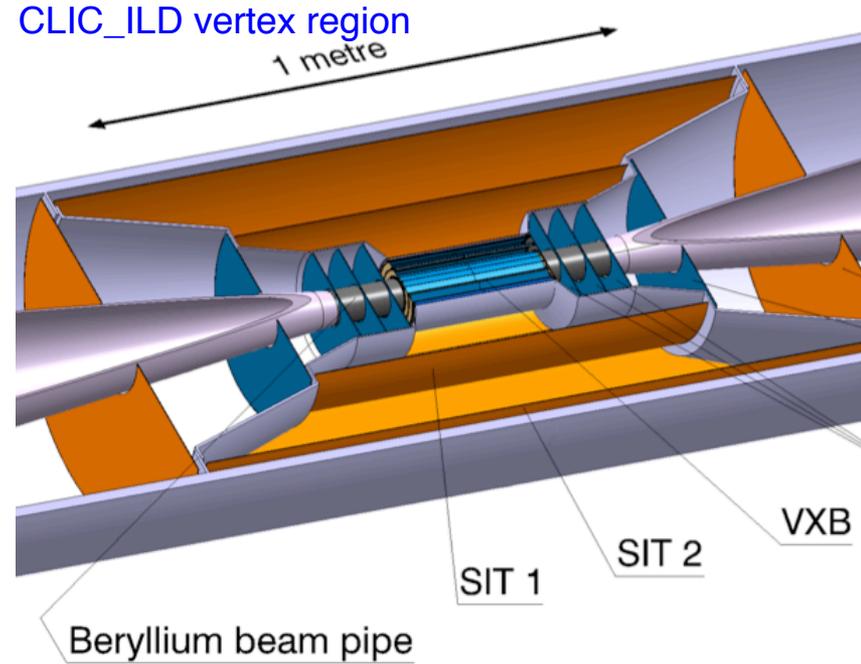
CLIC_ILD & CLIC_SiD

- detector concepts based on concepts developed for International Linear Collider (ILC):
- low-mass **vertex detector** with $\sim 25 \times 25 \mu\text{m}^2$ pixels
- **main trackers**: TPC + silicon (CLIC_ILD) or all silicon (CLIC_SiD)
- fine-grained **PFA calorimetry**, $1 + 7.5 \Lambda_i$
- **4-5 T solenoids**
- **return yoke** instrumented for muon ID
- complex **forward region** with final beam focussing

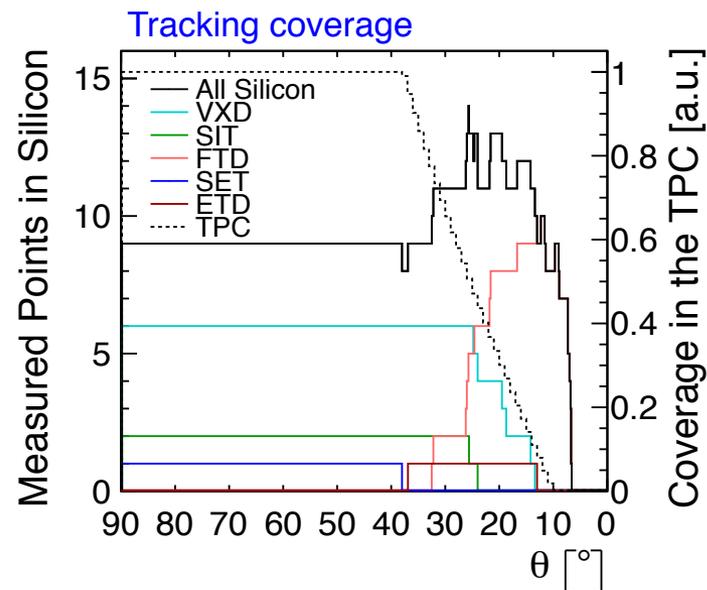
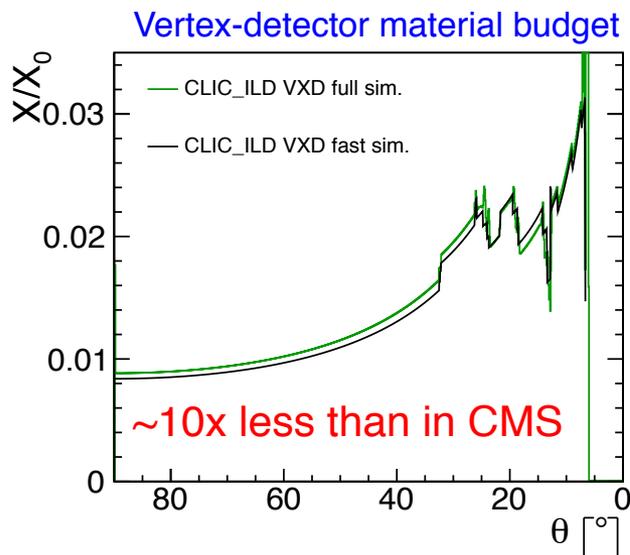


Vertex-detector concepts

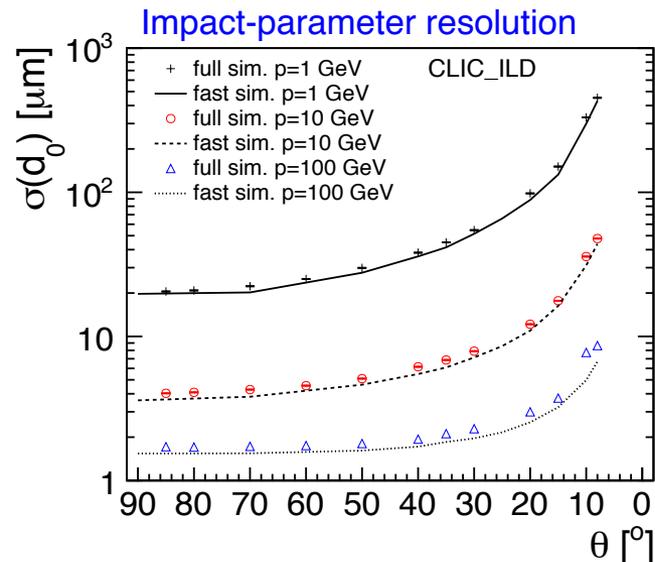
- barrel/end-cap layout
- 3 double layers or 5 single layers in central region
- 3 double layers or 7 single layers in forward region ($\theta > 7^\circ$)
- $\sim 25 \times 25 \mu\text{m}^2$ pixel size
- $\sim 1 \text{ m}^2$ area, $\sim 2 \text{ Gpixels}$
- $R_i \sim 27\text{-}31 \text{ mm}$
- beam pipes with conical sections
- optimized for high performance and low background occupancy



Performance in simulation



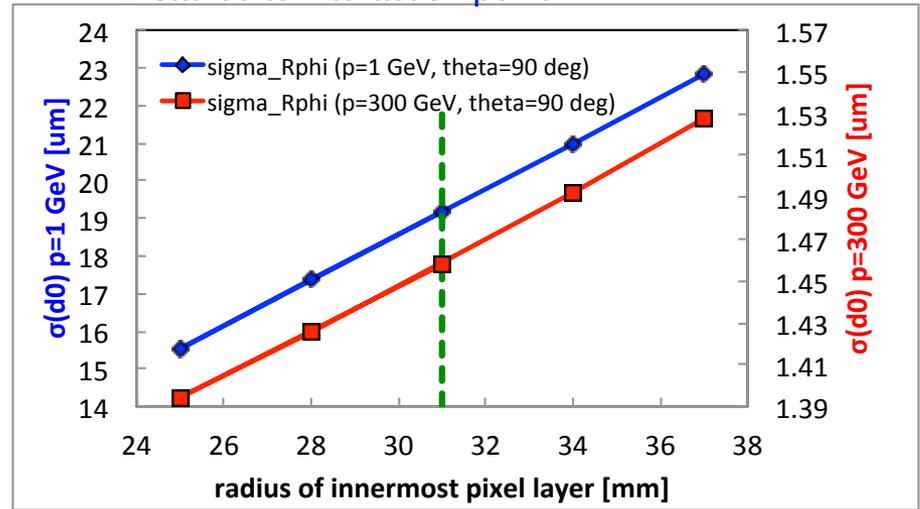
- Baseline **physics simulation** layouts:
 - very low material budget
 - large coverage
 - excellent performance in simulation
- **Engineering studies** add realism:
 - increased material budget
 - slightly reduced coverage
- Ongoing studies: assess impact of detector design on performance and develop **realistic simulation models**
 - parametric fast-simulation studies
 - flavor-tagging performance studies
 - impact on physics performance



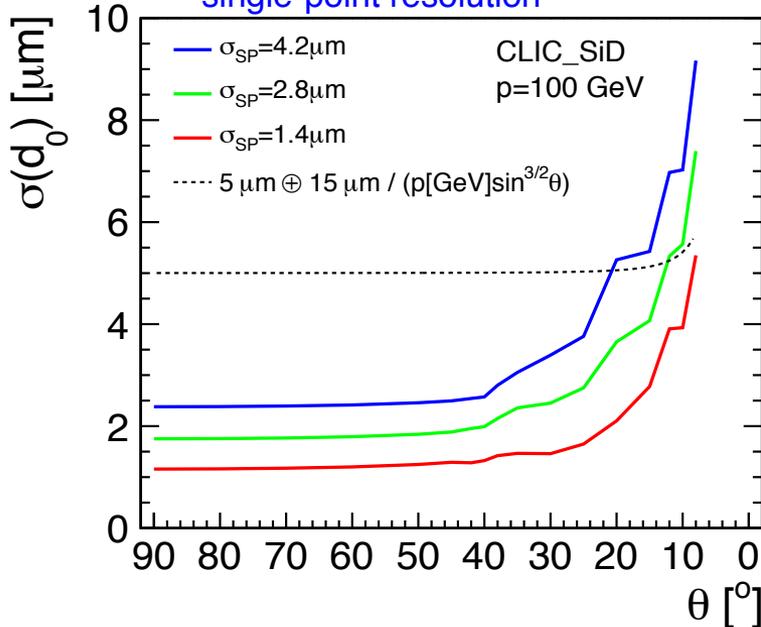
Parametric fast-simulation studies

- Parametric fast-simulation studies
- Main benchmark: transverse impact-parameter resolution $\sigma(d_0)$, closely linked to flavor-tagging perform.
- Assess influence of detector **geometry** and **technology** on $\sigma(d_0)$:
 - various detector layouts
 - different single-point resolutions
 - changes in material budget

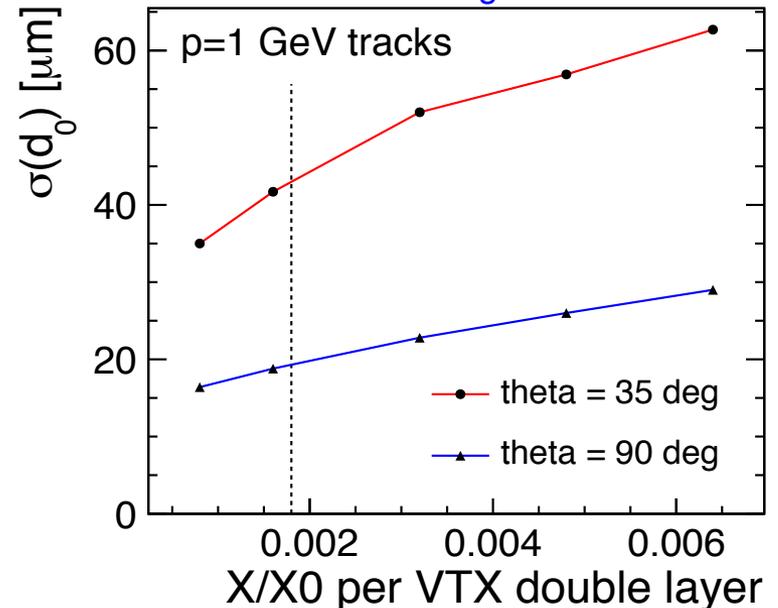
Distance to interaction point



single-point resolution



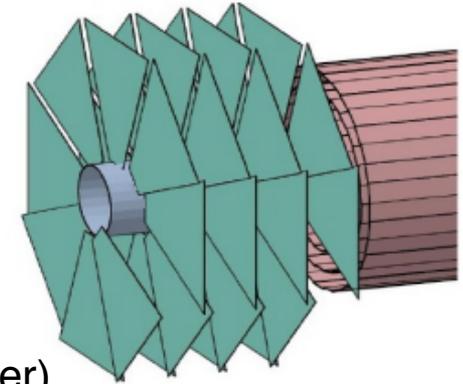
material budget



Flavor-tagging performance

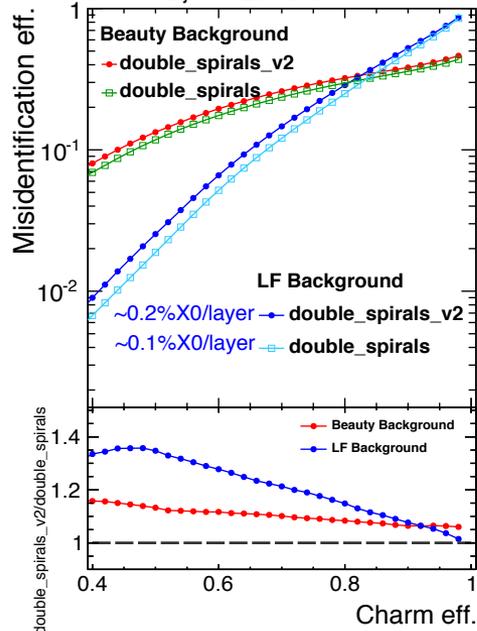
- Use **b- and c-tagging performance** as benchmark for detector designs
- Technically challenging full-simulation study (multivariate analysis)
- Results for geometries following engineering studies:
 - Geometry with **2x more material** in vertex layers
 - 5% - 35% degradation in performance
 - **Spiral end-cap** geometry (required for air-flow cooling)
 - few problematic regions with reduced coverage, otherwise similar performance as for disk geometry
 - **3 double layers** vs. **5 single layers**
 - small improvement for lower-energy jets (less material per layer)

CLIC_SiD spiral end-cap



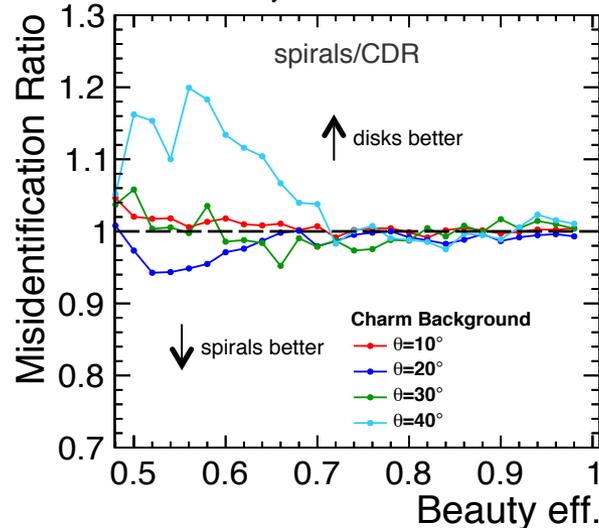
Material budget

Dijets at 200 GeV



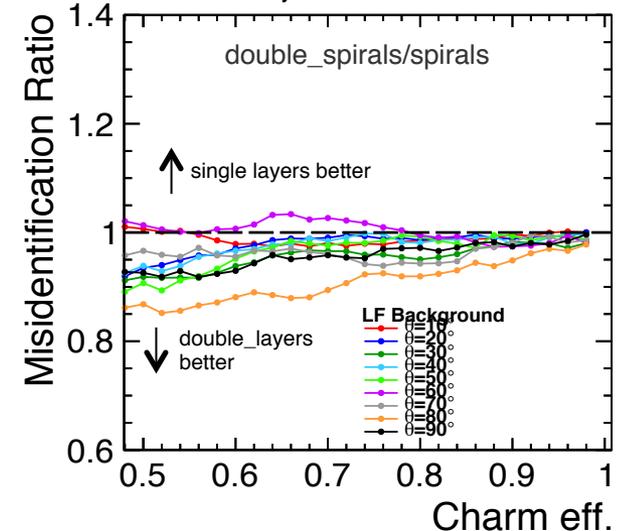
Spiral end-caps vs. disks

Dijets at 91 GeV



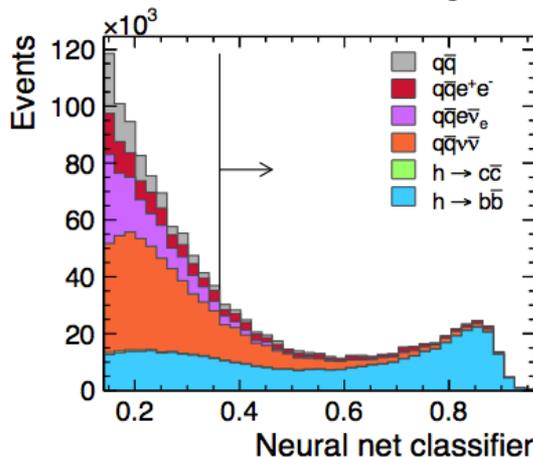
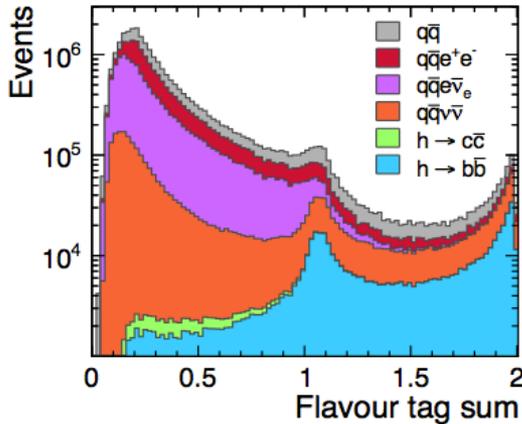
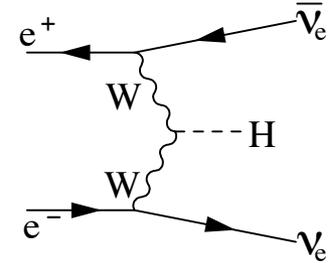
Double vs. single layers

Dijets at 91 GeV



Physics performance

- Ultimate benchmark for vertex-detector: impact on physics analysis results
- Example: achievable precision in $e^+e^- \rightarrow H\nu_e\bar{\nu}_e$, $H \rightarrow b\bar{b}, c\bar{c}$
 - Dominant Higgs-production process at 3 TeV
 - Large backgrounds from light-flavor decays
→ analysis depends strongly on b and c tagging



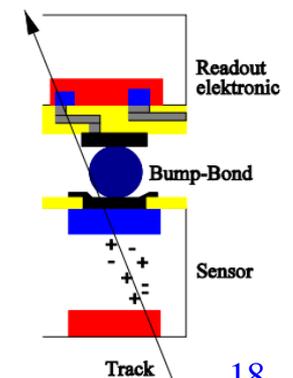
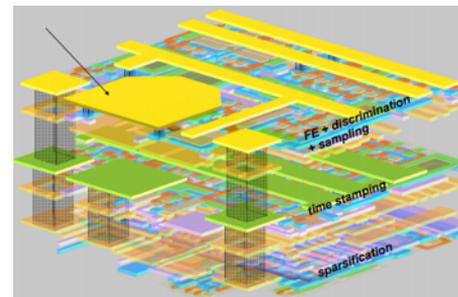
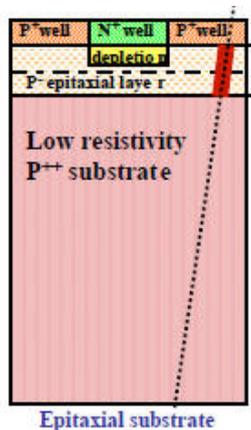
- Consider $\pm 20\%$ change in wrong-flavor rejection
- Dominant backgrounds:
 - $H \rightarrow b\bar{b}$: light flavor jets
 - $H \rightarrow c\bar{c}$: light flavor and b-jets
- Impact on achievable statistical precision for **cross-section x branching-ratio** measurements, for $\sqrt{s}=3$ TeV and $L_{int}=2$ ab $^{-1}$:

analysis	stat. uncert. on $\sigma \times BR$	change for $\pm 20\%$ fake rate
$H \rightarrow b\bar{b}$	0.23%	$\pm 6-7\%$
$H \rightarrow c\bar{c}$	3.1%	$\pm 15\%$

Pixel-detector technologies



	Monolithic	3D-integrated	Hybrid
Examples	FPCCD, MAPS, HV-CMOS	SOI, MIT-LL, Tezzaron, Ziptronix	Timepix3/CLICpix
Technology	Specialised HEP processes, r/o and sensors integrated	Customized niche industry processes, high density interconnects btw. tiers	Industry standard processes for readout; depleted high-res. planar or 3D sensors
Interconnect	Not needed	SLID, Micro bump bonding, Cu pillars	
granularity	down to 5 μm pixel size		$\sim 25 \mu\text{m}$ pixel size
Material budget	$\sim 50 \mu\text{m}$ total thickness achievable		$\sim 50 \mu\text{m}$ sensor + $\sim 50 \mu\text{m}$ r/o
Depletion layer	partial	partial or full	full \rightarrow large+fast signals
timing	Coarse (integrating sensor)	Coarse or fast, depending on implementation	Fast sparsified readout, $\sim \text{ns}$ time slicing possible
R&D examples	ILC, ALICE, RHIC	ILC, HL-LHC	CLIC, ATLAS-IBL, HL-LHC



Medipix/Timepix hybrid r/o chip family



Chip	Year	CMOS Process	Pitch [μm^2]	Pixel operation modes	r/o mode	Main applications
Timepix	2006	250 nm	55x55	\int TOT or ToA or γ counting	Sequential (full frame)	HEP (TPC)
Medipix3RX	2012	130 nm	55x55	γ counting	Sequential (full frame)	Medical
Timepix3	2013	130 nm	55x55	TOT + ToA, γ counting + \int TOT	Data driven	HEP, Medical
Smallpix	2014	130 nm	\sim 40x40	TOT + ToA, γ counting + \int TOT	Sequential (data comp.)	HEP, Medical
CLICpix demonstrator	2013	65 nm	25x25	TOT + ToA	Sequential (data comp.)	Test chip with 64x64 pixel matrix
CLICpix	tbd	65 nm	25x25	TOT + ToA	Sequential (data comp.)	CLIC vertex detector

TOT: Time-Over-Threshold

→ Energy

ToA: Time-of-Arrival

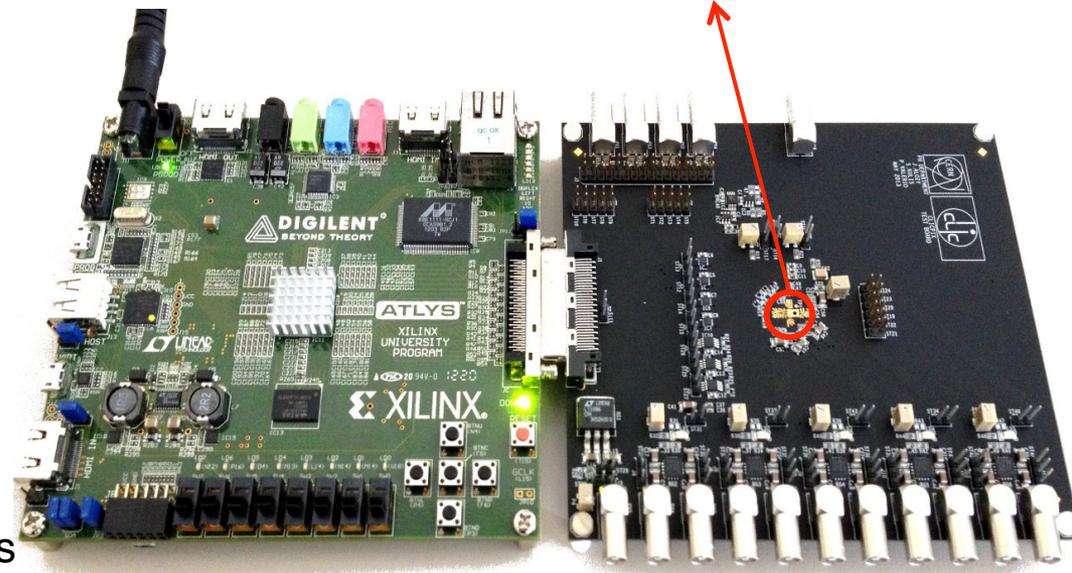
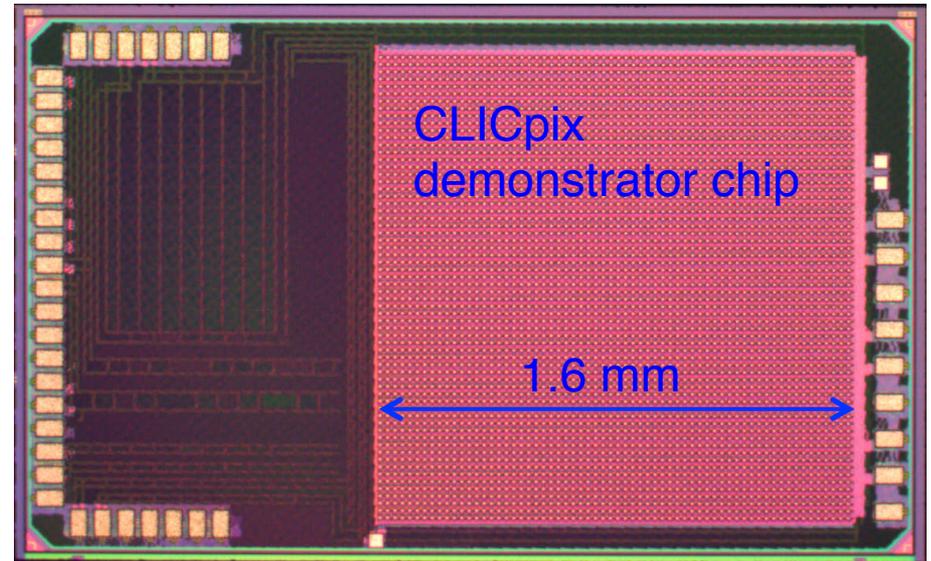
→ Time stamping

- Taking advantage of smaller feature sizes:
 - Increased functionality and/or
 - Reduced pixel size
 - Improved noise performance

Hybrid r/o technology: CLICPix

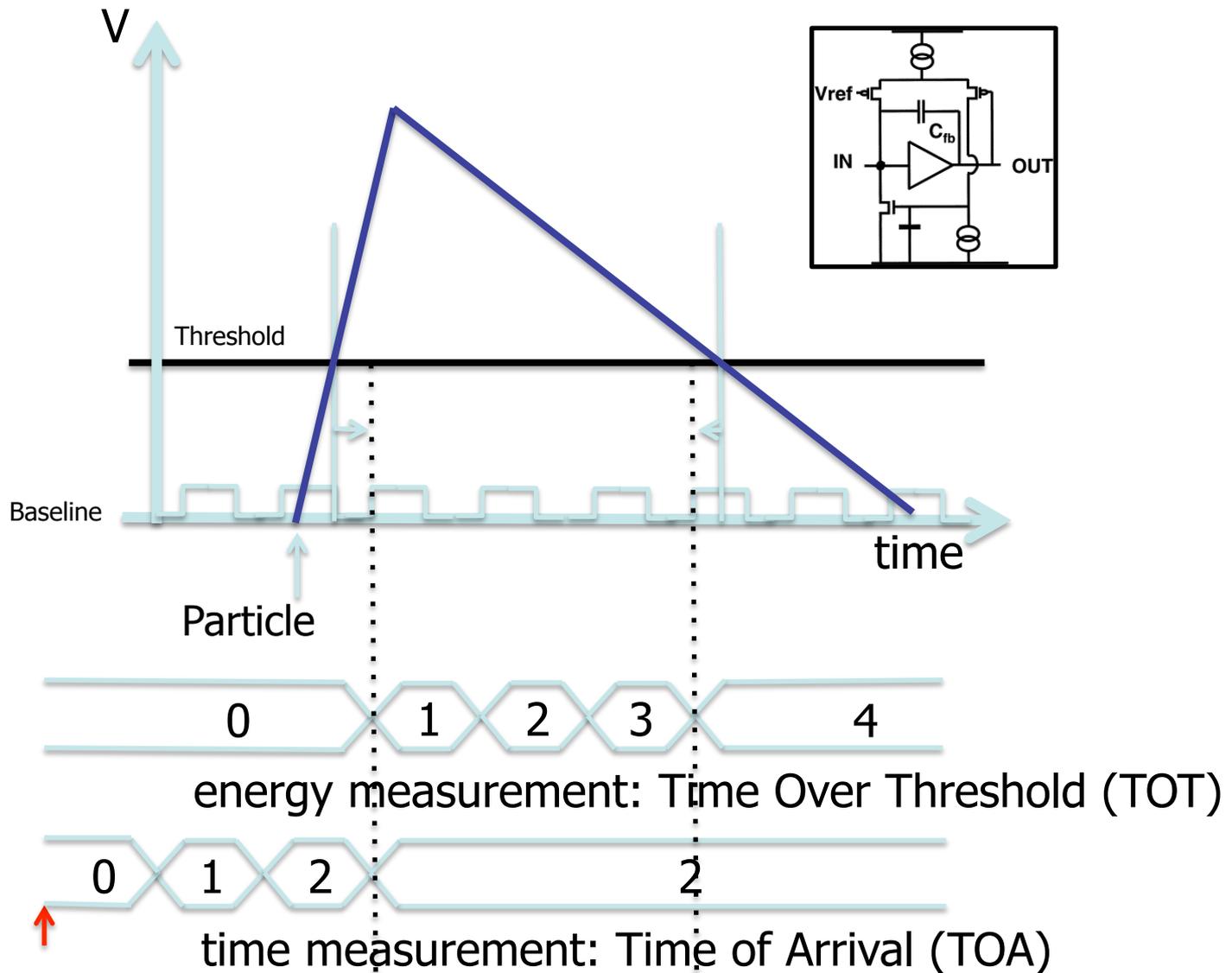


- **65 nm CMOS hybrid r/o chip**, targeted to CLIC vertex detectors
- based on **Timepix/Medipix** chip family, synergy with HL-LHC pixel r/o projects (**RD 53** collaboration on 65 nm r/o)
- **demonstrator chip** produced with fully functional 64 x 64 pixel matrix
- **25 μm** pixel pitch
- simultaneous **4-bit time (TOA)** and **energy (TOT)** measurement per pixel
- front-end **time slicing < 10 ns**
- selectable **compression** logic: pixel, cluster + column-based
- full chip r/o in less than 800 μs (at 10% occup., 320 MHz r/o clk)
- **power pulsing scheme**
- $P_{\text{avg}} < 50 \text{ mW/cm}^2$
- **r/o tests on prototypes:**
 - chip fully functional
 - measurements confirm simulations

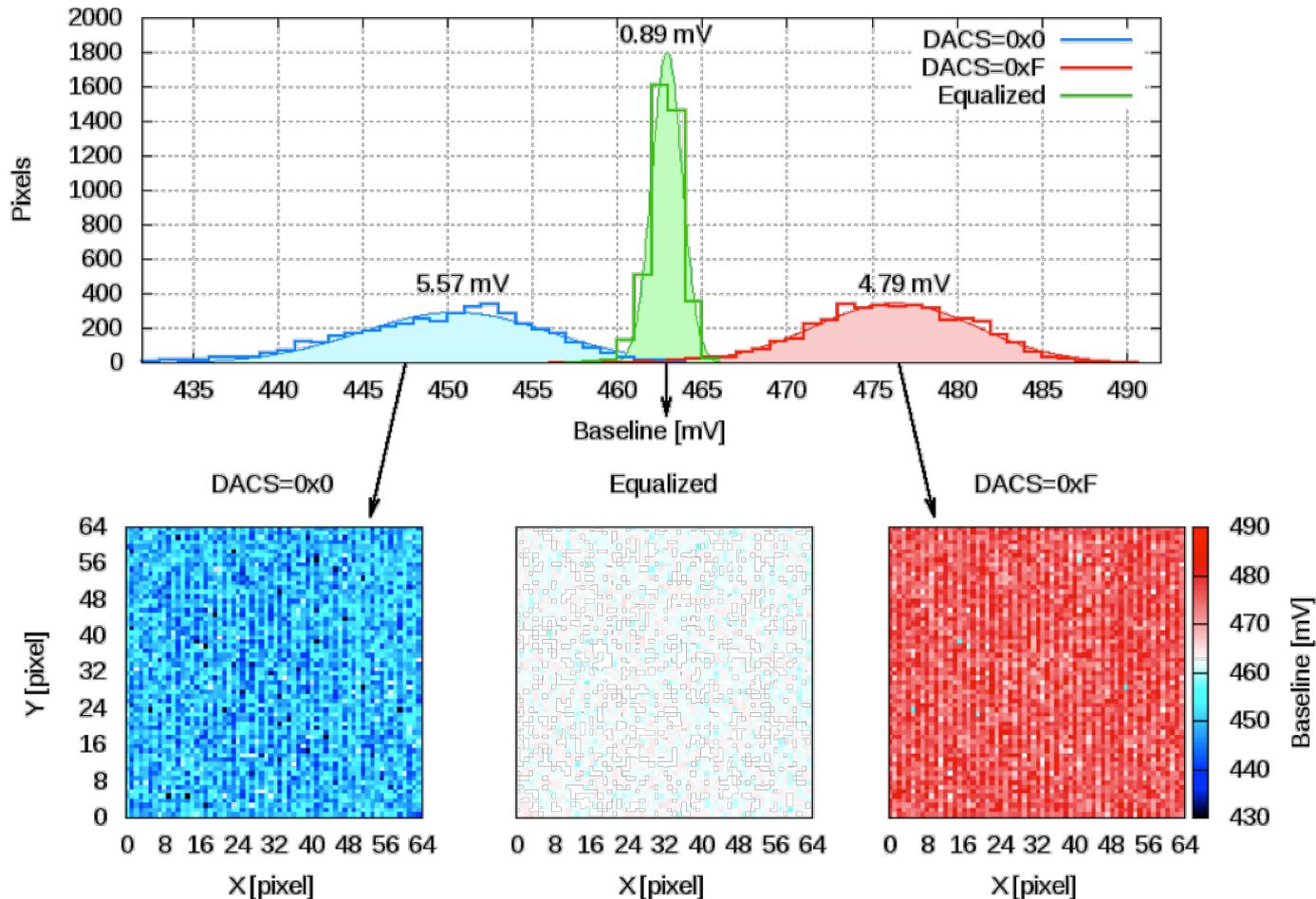


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CLICpix: time and energy measurement



CLICpix: baseline equalization

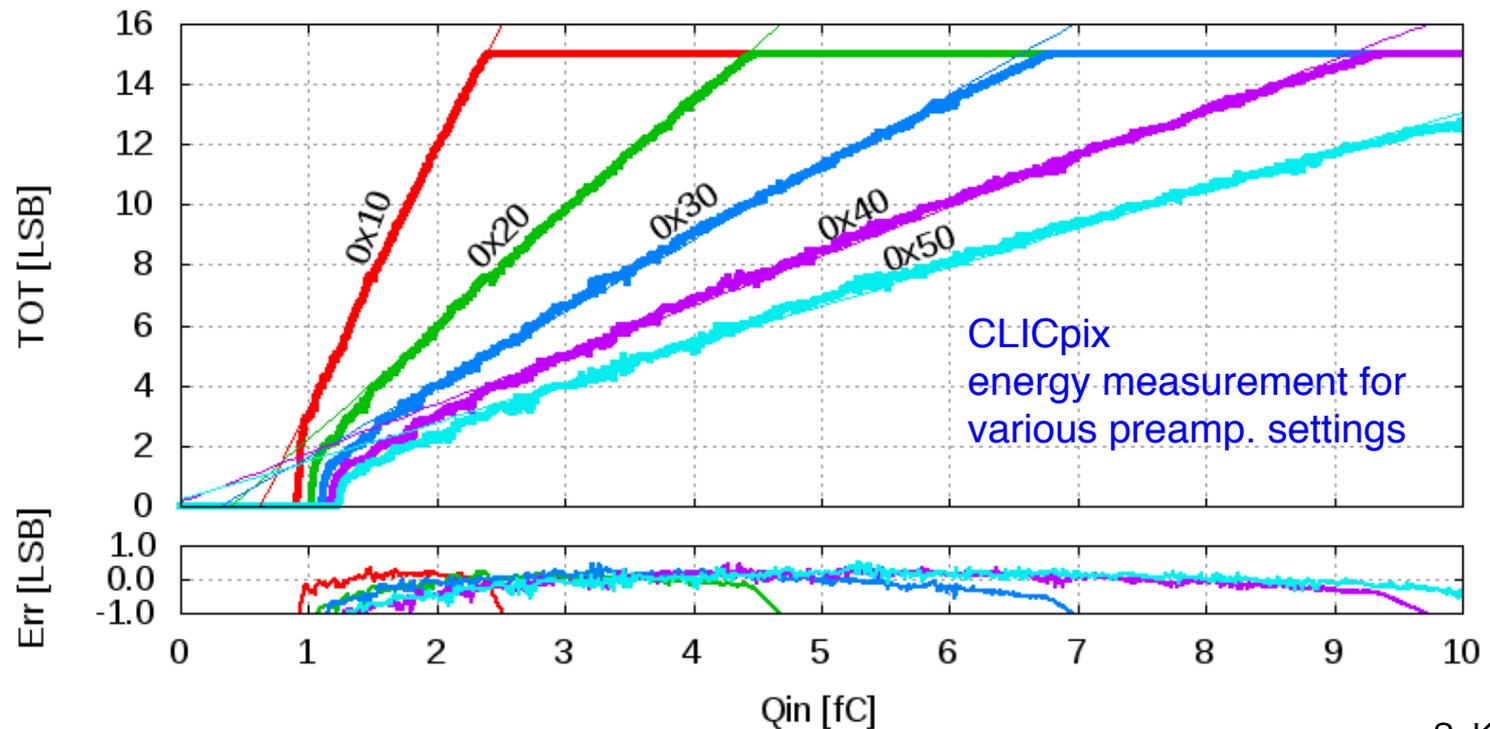


Calibrated spread is 0.89 mV (about 22 e-) across the whole matrix

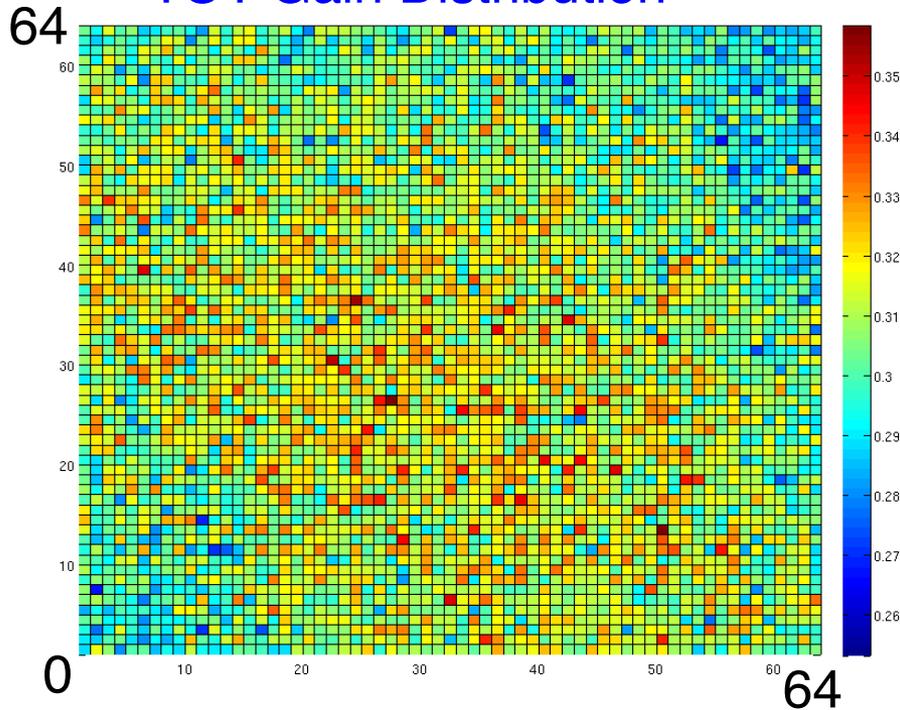
CLICpix: energy measurement



- Measure charge released in each pixel
→ Improve position resolution through interpolation
- Time-Over-Threshold (TOT) measurement (4-bit precision)
- Calibration measurement using external test pulser:

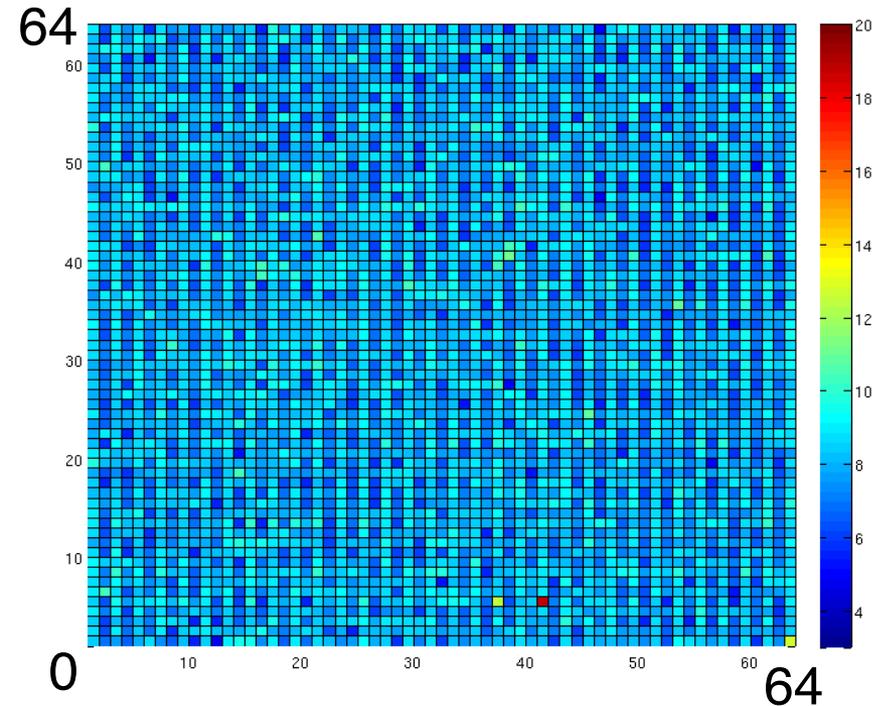


TOT Gain Distribution



- Uniform gain across the matrix
- Gain variation $\sim 4.2\%$ r.m.s.
(for nominal feedback current)

Equivalent Noise Charge



- Uniform ENC across the matrix
- Mean ENC $\sim 55 e^-$
(without sensor)

CLICpix: summary



Parameter	Unit	Simulation	Measurement
Rise time	[ns]	50	-
TOA accuracy	[ns]	<10	<10
Gain	[mV/ke ⁻]	44	40 *)
Dynamic range	[ke ⁻]	44 (configurable)	40 *) (configurable)
INL (TOT)	[LSB]	<0.5	<0.5
ENC (w/o sensor)	[e ⁻]	~60	~55 *)
DC spread σ (uncalibrated)	[e ⁻]	160	128 *)
DC spread σ (calibrated)	[e ⁻]	24	22 *)
Power consumption	[μ W/pixel]	6.5	7

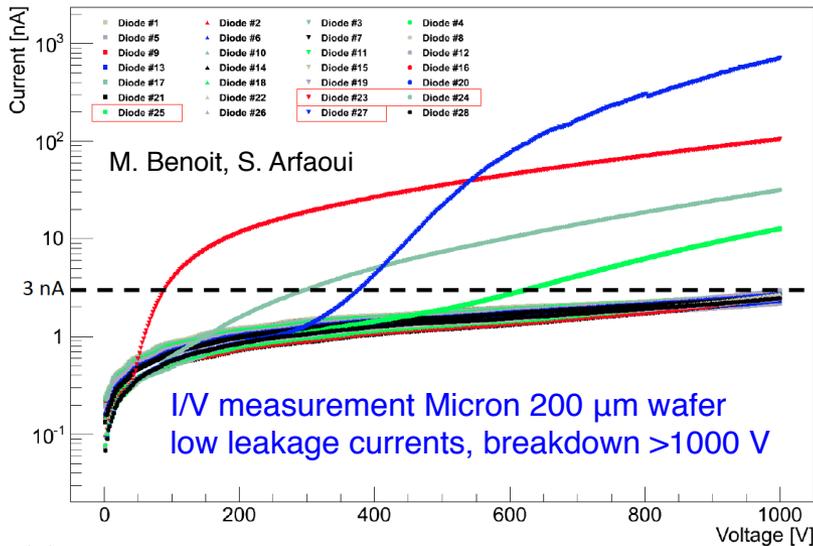
*) results obtained with electrical test pulses

- good agreement between simulations and measurements
- power pulsing works according to specifications (>10x reduction for power-off state)
- programmable power on/off times, front-end wake up within ~15 μ s
- Radiation test ongoing (up to 1 GRad TID)

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Thin-sensors

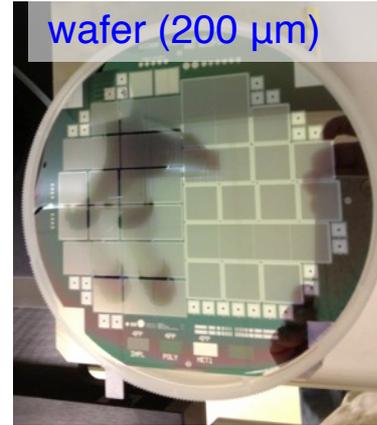
- Micron (UK) + IZM (DE) and VTT/Advacam (FI)
Timepix planar sensor assemblies with 55 μm pitch
 - Test feasibility of ultra-thin sensors and assemblies
 - Assemblies delivered: 50-200 μm sensor thickness, 100-450 μm ASIC thickness
 - Test beams at DESY in 2013
 - Sensor calibration (non-linear TOT response)
- sensors matching 25 μm^2 CLICpix footprint \rightarrow 2014
- ultimate goal: 50 μm thick sensors + 50 μm thick ASICs



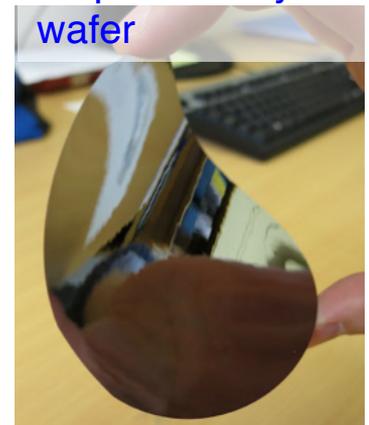
Alternative sensor concepts:

- Low-Gain Avalanche Detectors (LGAD) with charge multiplication
 \rightarrow thin sensors with large and fast signals (RD50 project with CNM)
- HVCMOS CCPD with capacitive coupling
 \rightarrow no more bump bonding necessary

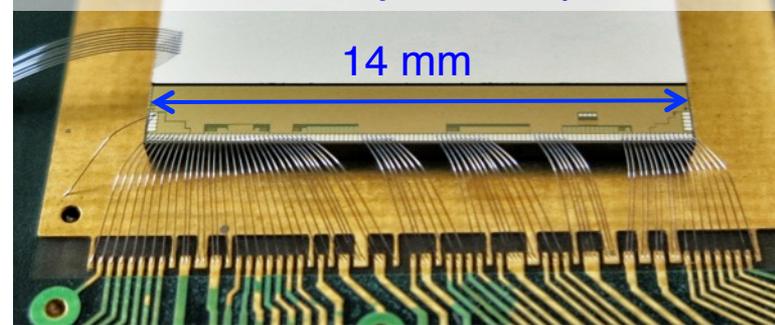
Micron sensor wafer (200 μm)



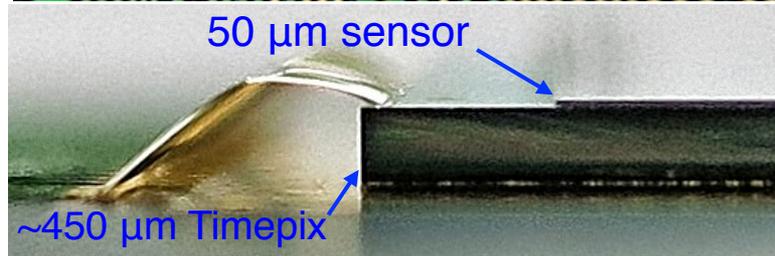
50 μm dummy wafer



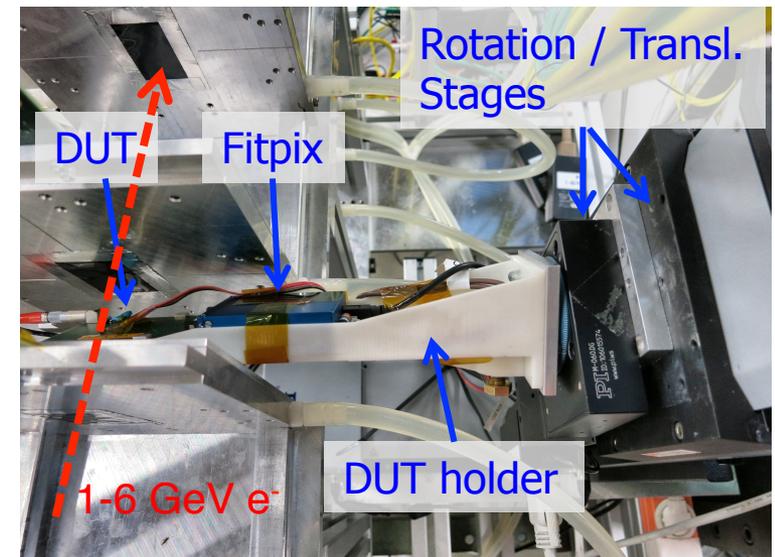
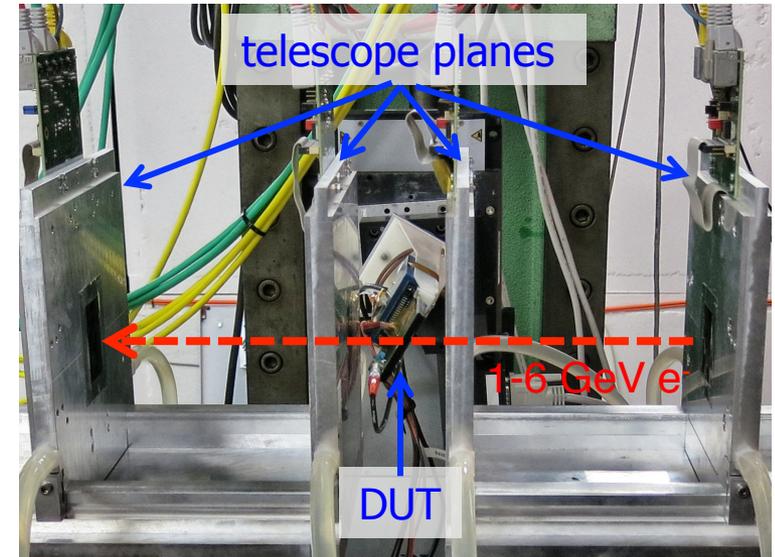
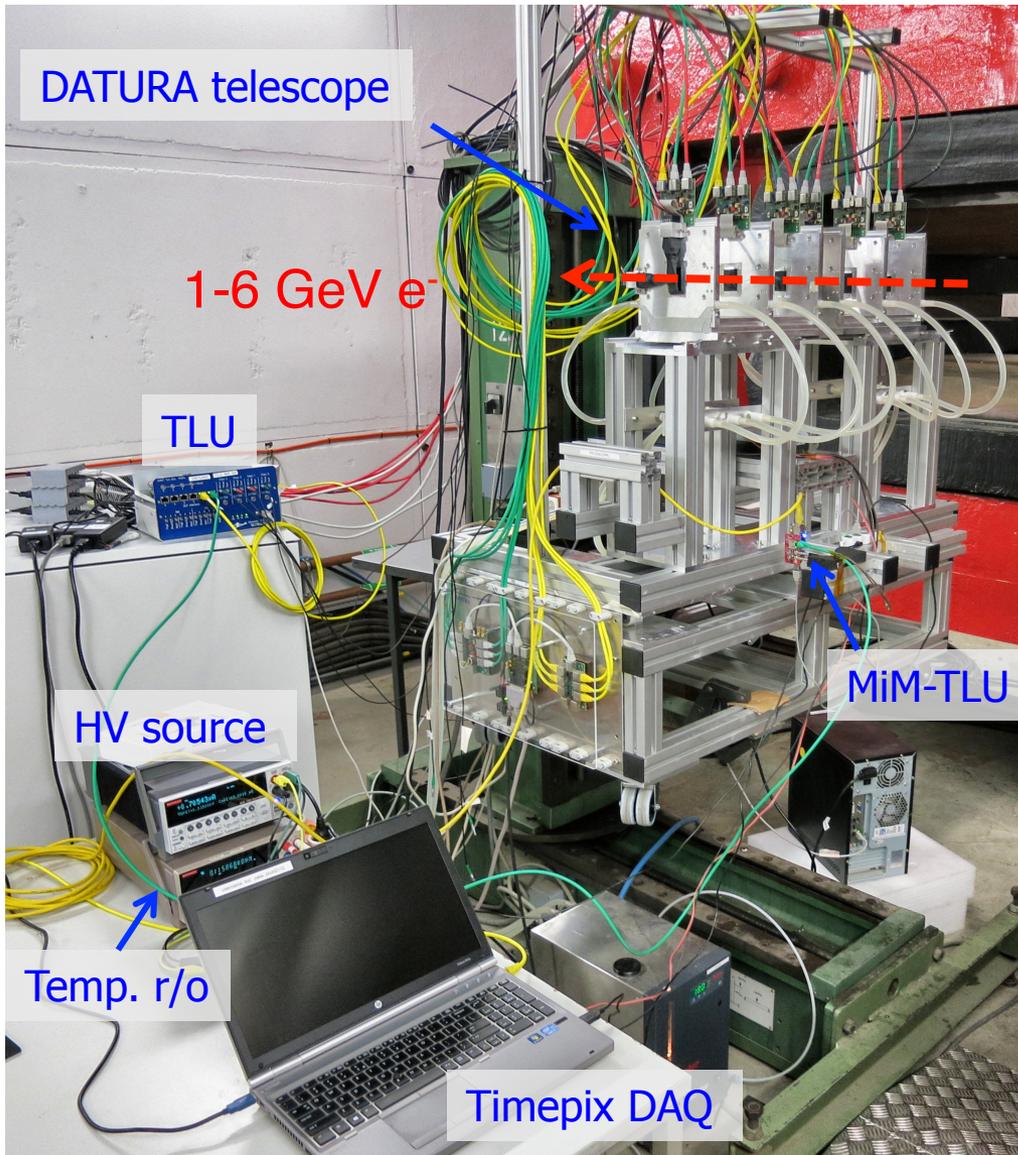
Advacam assembly with 50 μm sensor



50 μm sensor



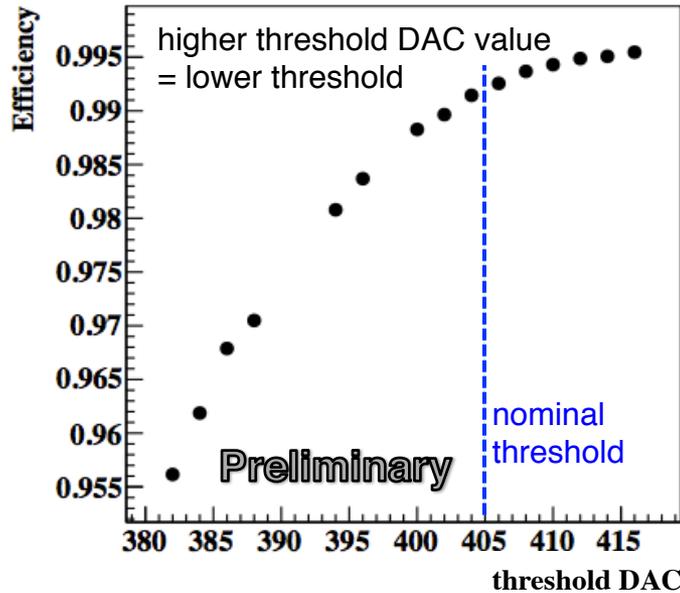
Test beam setup at DESY



Thin-sensor assemblies in test beam



Threshold scan Advacam 50 μm active edge

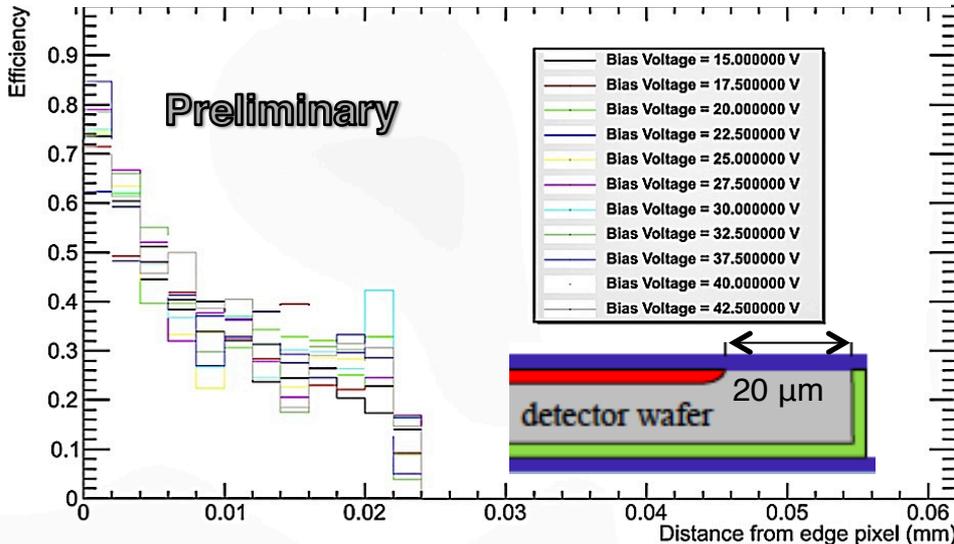


Measurements in DESY II 5.5 GeV e^- beam using DATURA Telescope

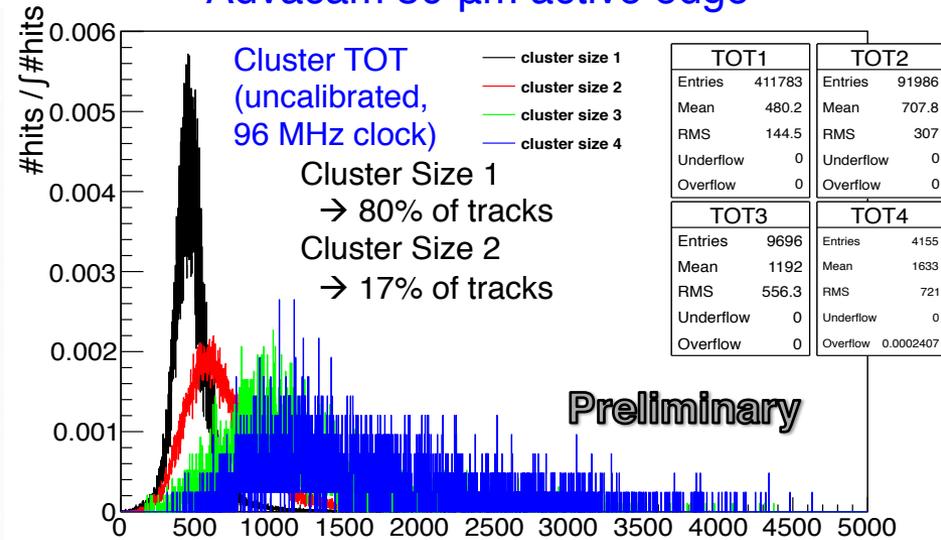
- Assemblies with Advacam p-in-n sensors,
- 50 μm thick, 55 μm pitch
- 20 μm or 50 μm active edges
- Bonded to 450 μm Timepix r/o chip
- Overall Efficiency > 99% (no fiducial cuts)
- Efficiency extends beyond last pixel row

M. Benoit, S. Redford, et al.

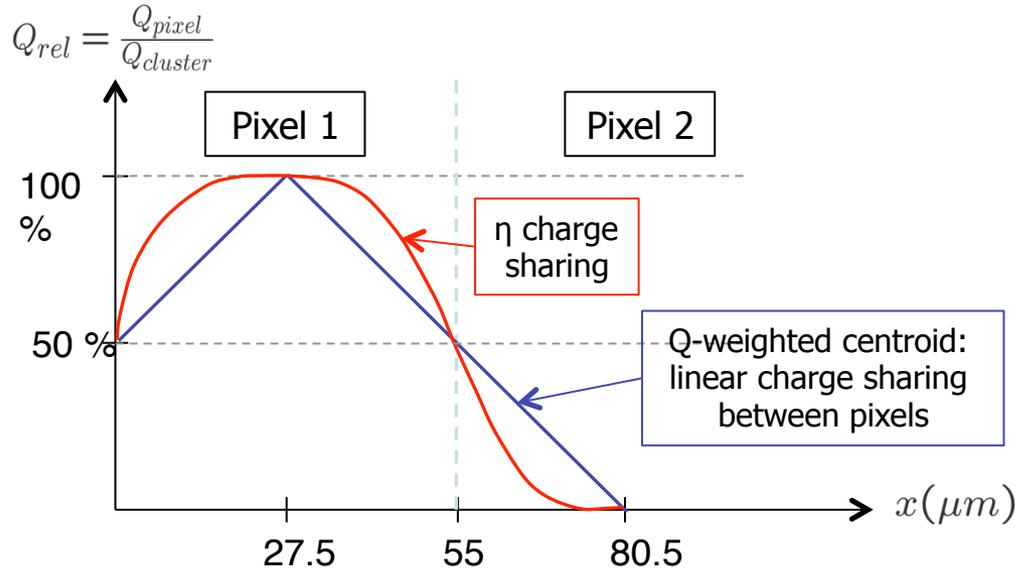
Edge efficiency Advacam 20 μm active edge



Advacam 50 μm active edge



Charge sharing



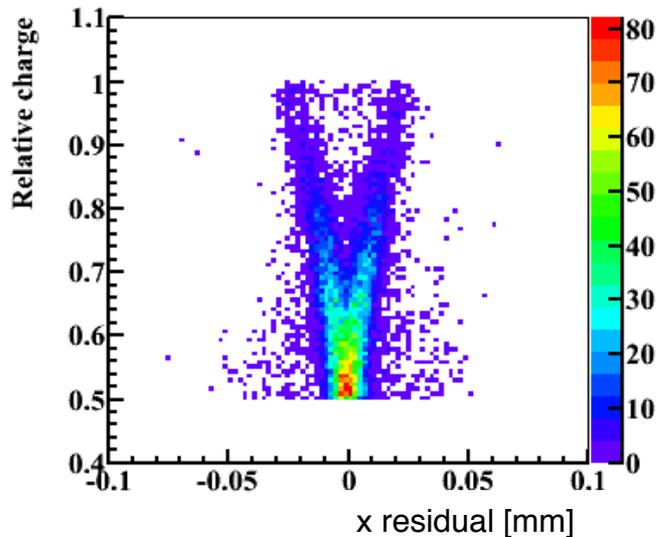
- Non linear charge sharing between pixels, parameterized by η function:

$$\eta(x) = Q_{cluster} \times \frac{\text{erf}(\frac{x}{\sigma}) + 1}{2} \quad \text{if } x < \text{pitch}X/2$$

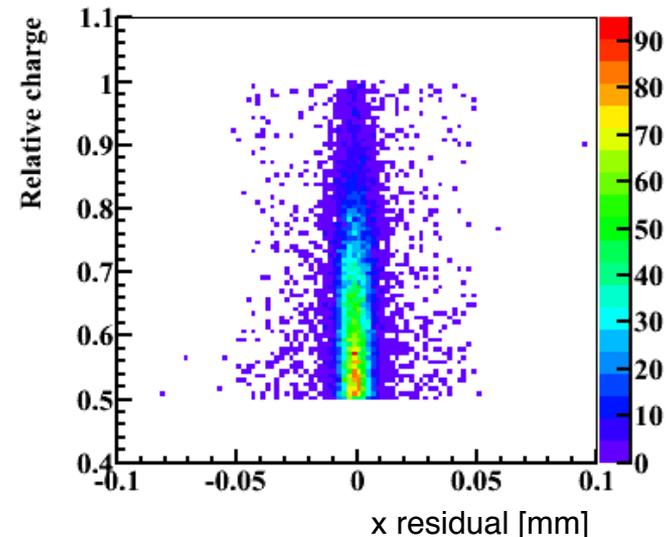
$$\eta(x) = Q_{cluster} \times \frac{\text{erf}(\frac{\text{pitch}X - x}{\sigma}) + 1}{2} \quad \text{if } x > \text{pitch}X/2$$

- Single parameter σ describing diffusion of charge cloud in electric field
- Obtain σ from minimization of position resolution

Linear interpolation



η correction



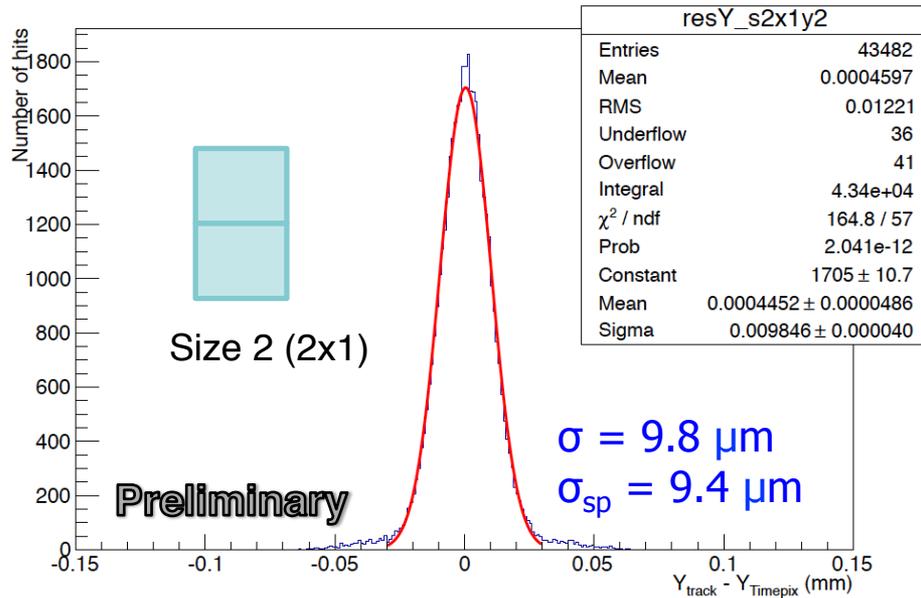
Resolution with eta correction



- Comparison linear interpolation / η correction for 2-hit clusters (17% of all tracks):
 - $\sigma_{SP} \sim 9 \mu\text{m}$ for linear interpolation
 - $\sigma_{SP} \sim 3 \mu\text{m}$ with η correction
- Note: selection bias of 2-hit clusters not unfolded

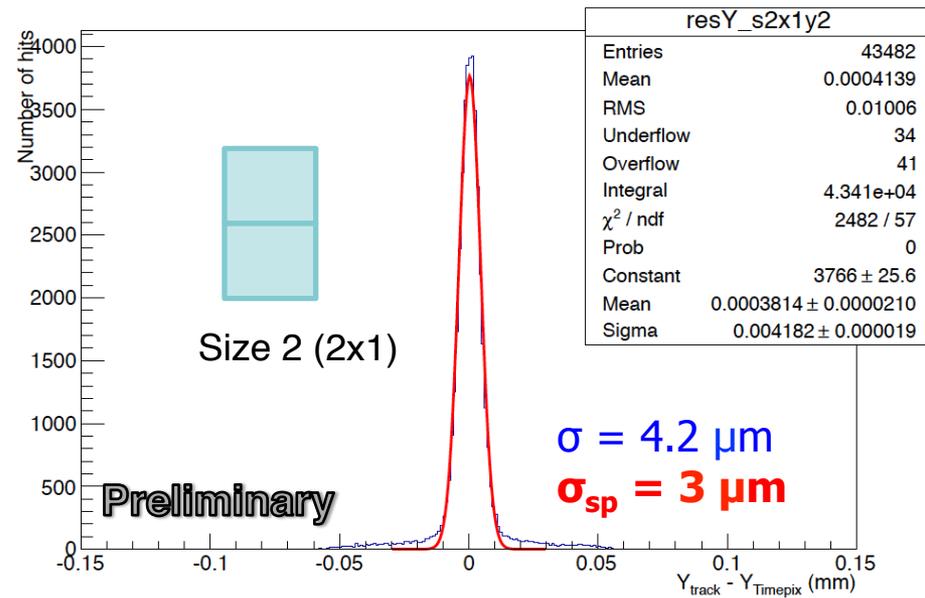
Linear interpolation

Unbiased residual Y, cluster size = 2, sizeX = 1 and sizeY = 2



η correction

Unbiased residual Y, cluster size = 2, sizeX = 1 and sizeY = 2

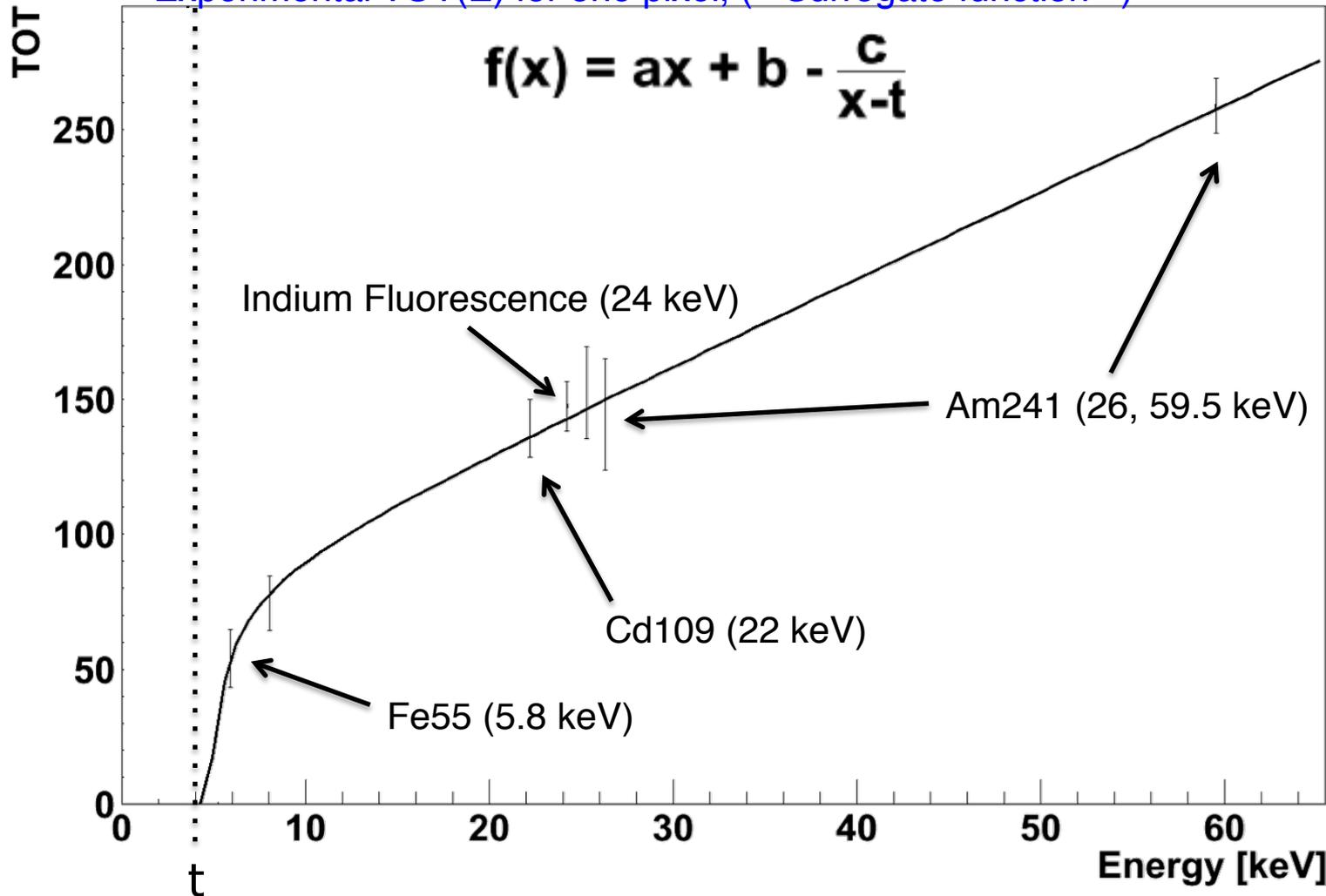


M. Benoit et al.

Timepix calibration

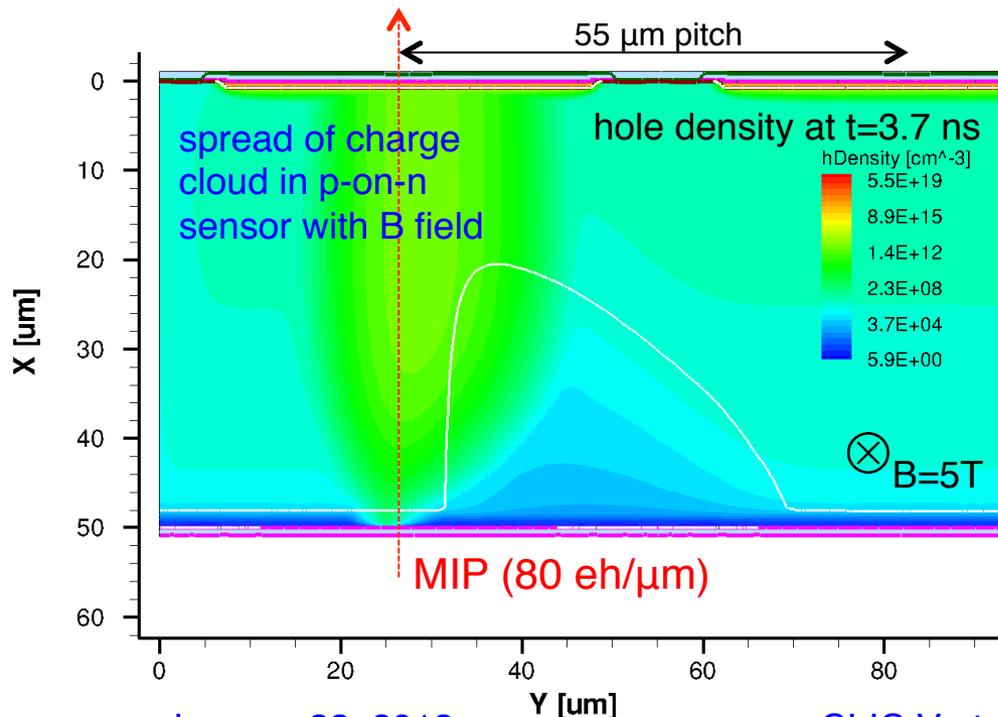
- Calibration of non-linear Timepix energy response with radioactive sources + fluorescence
- Parameterization with 4 parameters **per pixel**
- Improves accuracy of position determination with charge-weighting methods

Experimental TOT(E) for one pixel, (« Surrogate function »)

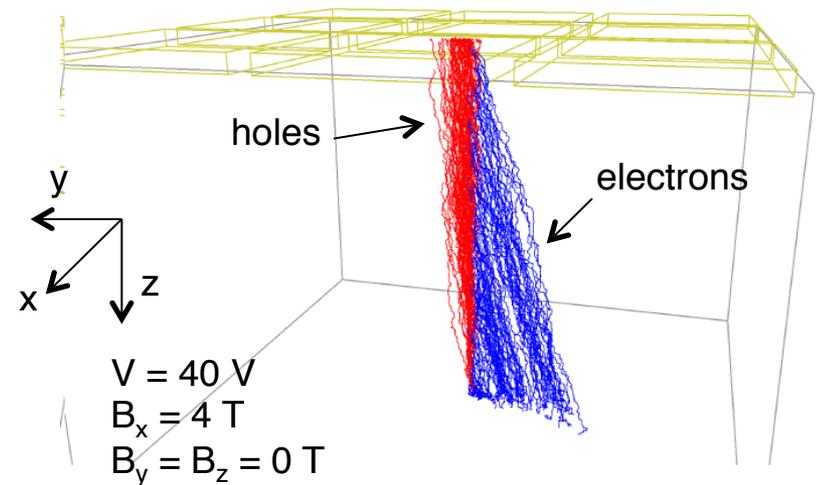


Simulations

- TCAD and MC simulations of charge propagation in silicon sensors
 - effect of sensor layout and material
 - effect of E and B fields (Lorentz angle)
 - comparison with lab and test-beam measurements
 - tuning of digitization models for full-detector simulation
- ALLPix general purpose pixel detector simulation and digitisation framework
 - used for simulation of test-beam and lab measurements
 - One-day tutorial at CERN on January 24th



Carrier drift in 50 μm thick fully depleted sensor:

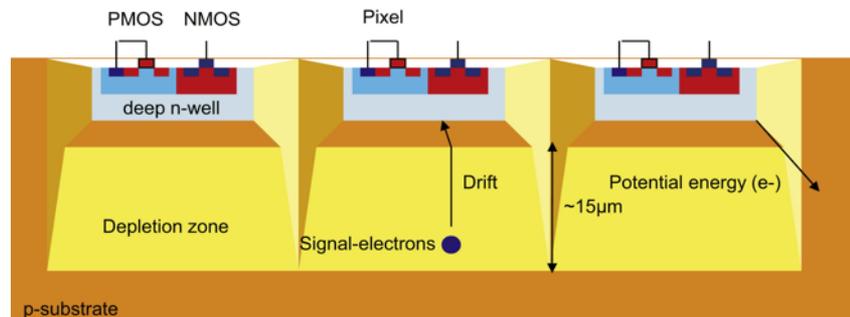


Integrated / hybrid technology: HV-CMOS



HV-CMOS MAPS:

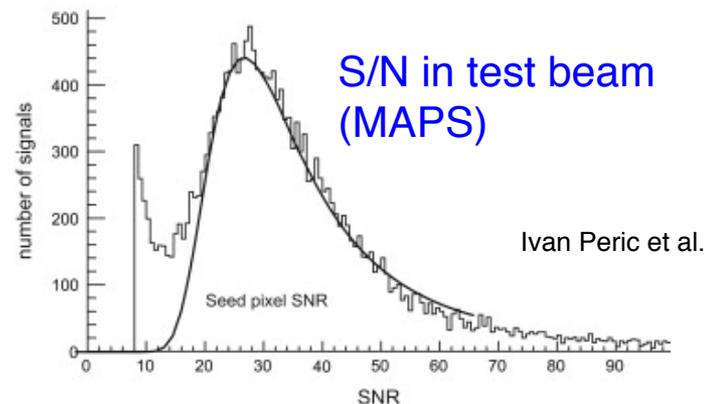
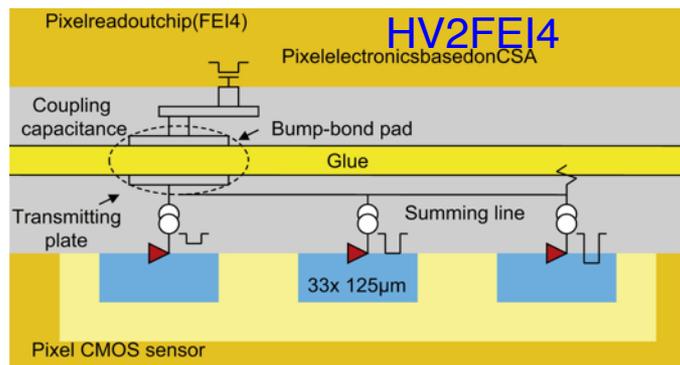
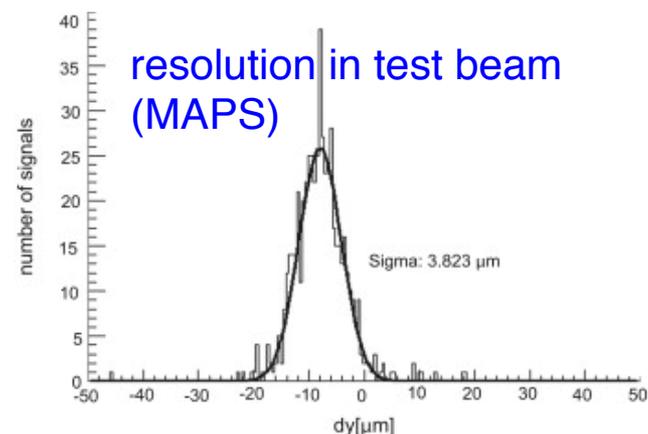
- 180 nm High-Voltage CMOS process:
Vbias~100 V → depletion layer ~10-20 μm
- **integrated** sensors with fast signal collection
- baseline technology for Mu3e at PSI



Hybrid option:

Capacitive Coupled Pixel Detector (CCPD)

- HV-CMOS chip as integrated sensor+amplifier
- **capacitive coupling** from amplifier output to r/o chip through layer of glue → no bump bonding!
- test chip for ATLAS FEI4 and Timepix produced
- proof of principle measurements



Heidelberg, CERN, CPPM, Bonn, Geneva, Glasgow

January 22, 2013

CLIC Vertex R&D

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HV-CMOS ATLAS/CLICpix prototype CCPDV3



New HVCMOS prototype,
to test capacitive coupling
with CLICpix demonstrator

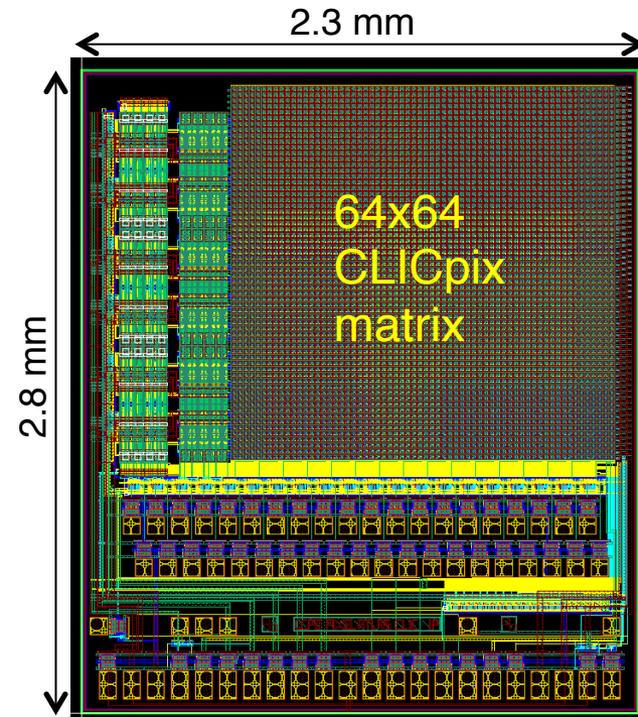
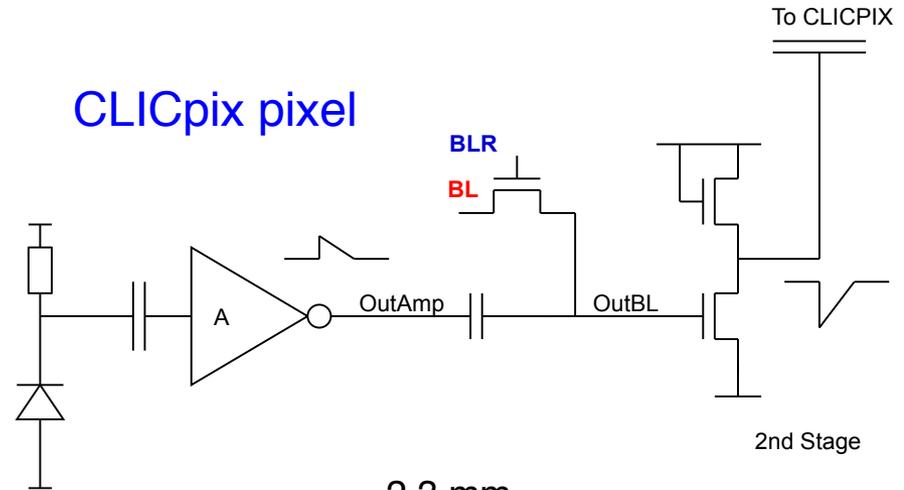
6.4 mm² split in
ATLAS FEI4 + CLICpix parts

Includes 64x64 CLICpix
matrix with 25 μm pitch

2-stage amplifier

AMS H18 180 nm process

Submission November 2013



CCPDV3

Ivan Peric

Through-Silicon Vias (TSV)

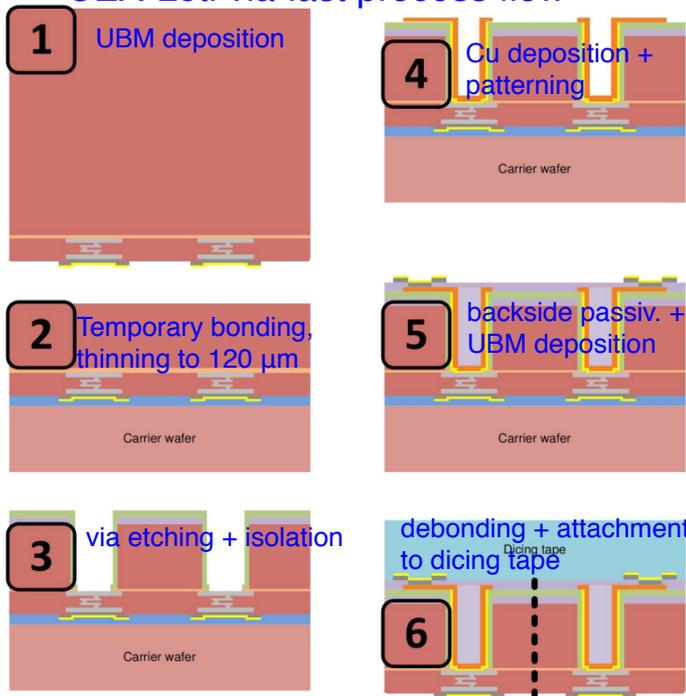
Through Silicon Via (TSV): **vertical electrical connection** passing through Si wafer

- eliminates need for wirebonds
- 4-side buttable chips
- increased reliability, reduced material budget

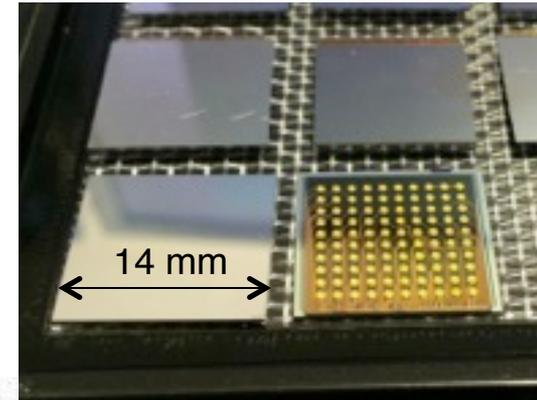
Example: **Medipix TSV project** (ALICE, CLIC, ACEOLE and AIDA) with **CEA-Leti**

- 130 nm IBM Medipix(RX) wafers, via-last process
- successful completion of first phase: demonstrate **feasibility**
- on-going second phase: demonstrate **good yield**

CEA-Leti via-last process flow



- 240 μm TSV diameter
- wafers thinned to 120 μm
- 5 μm copper layer for TSV



First Medipix3 Image taken with TSV assembly:



Medipix Collaboration + CEA-Leti

CLICpix power-pulsing + delivery requirements

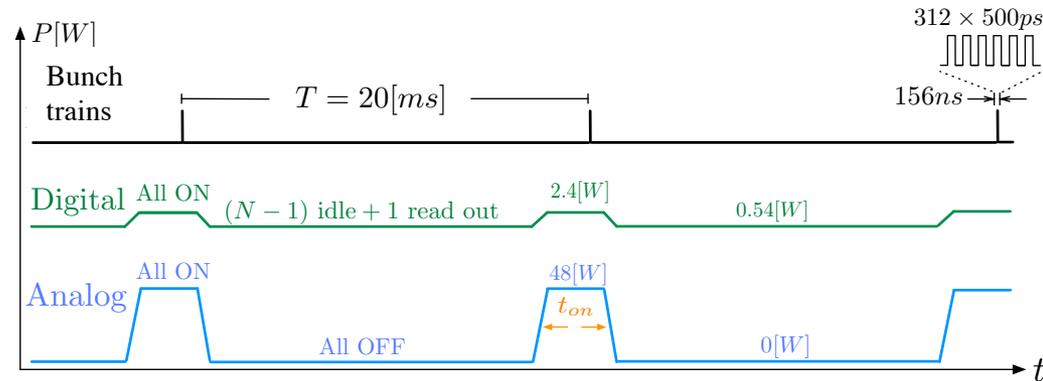


Small duty cycle of CLIC machine allows for power reduction of readout electronics: turn off front end in gaps between bunch trains

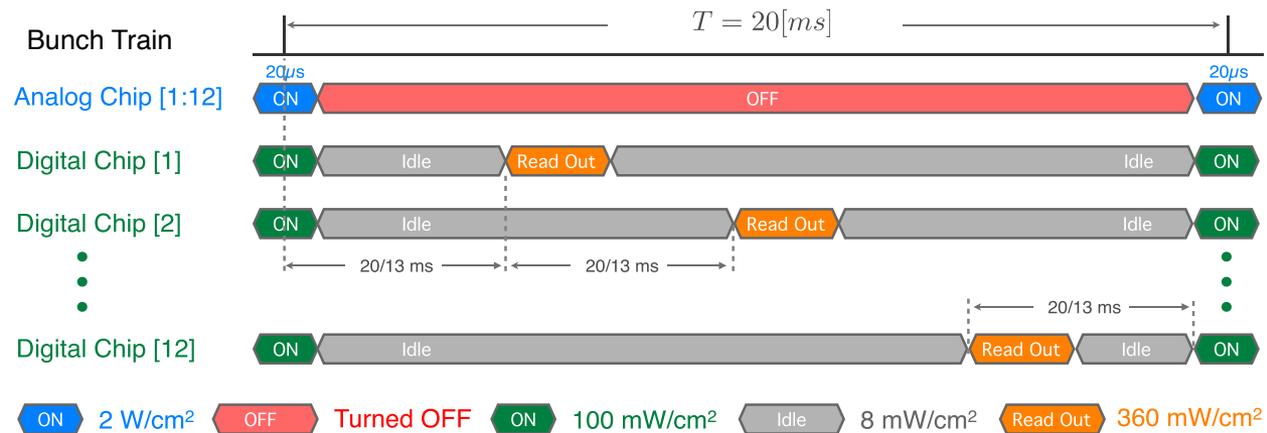
Challenging requirements:

- Power budget **<50 mW/cm²** average (air-flow cooling limit)
- High peak current **> 40A/ladder**
- Different timing analog/digital electronics
- High magnetic field **4-5T**
 and
- Material budget **< 0.1% X₀** for services+supports
- Regulation **< 5% (60 mV)** for analog part

Vertex-detector power consumption



CLICpix powering states

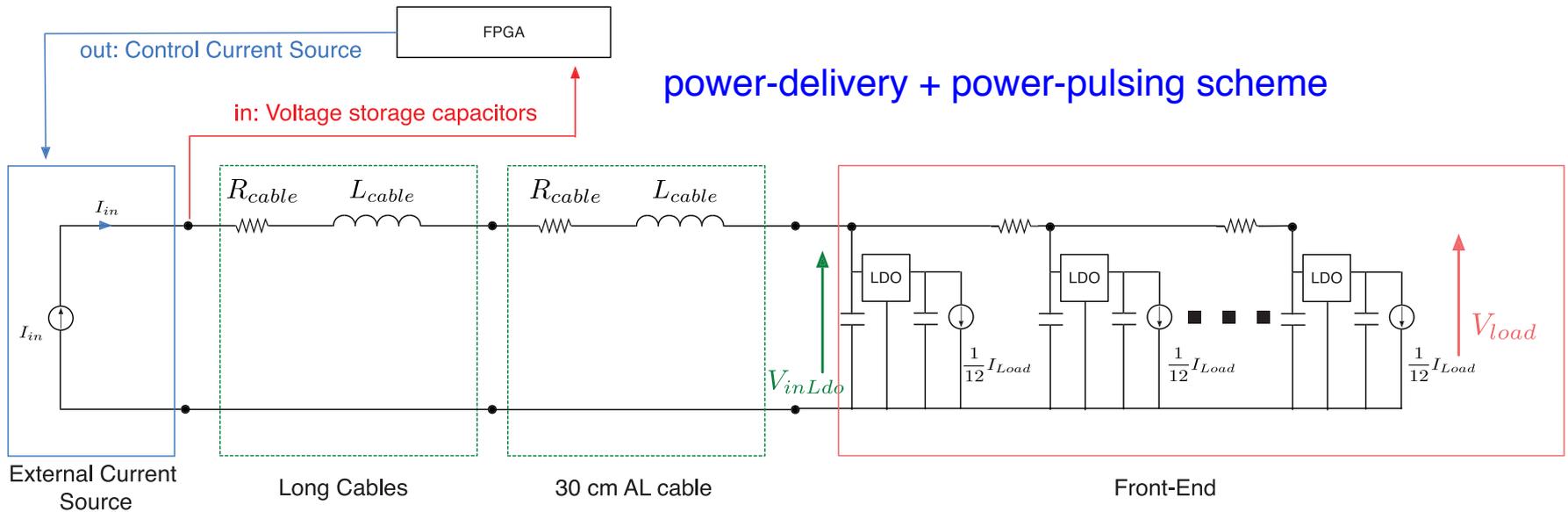


C. Fuentes, X. Llopart, P. Valerio

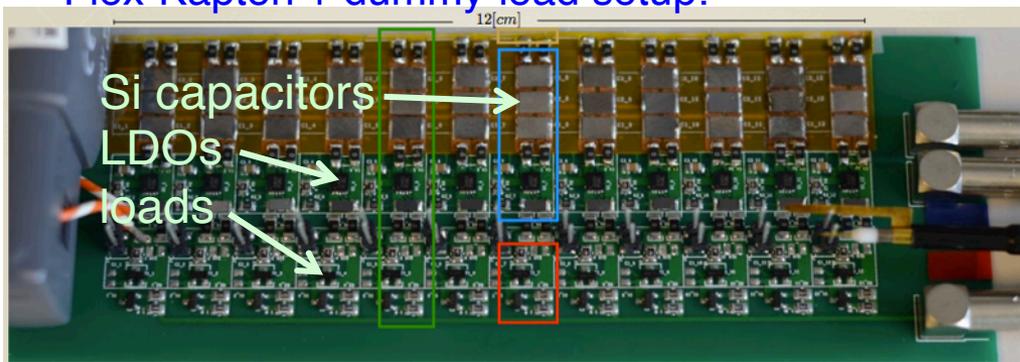
CLICpix power-pulsing + delivery concept



power-delivery + power-pulsing scheme



Flex-Kapton + dummy-load setup:

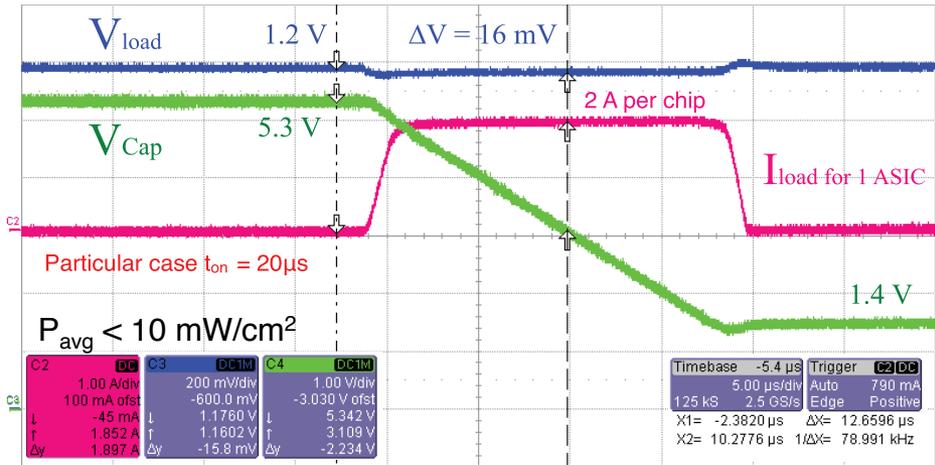


- Power pulsing with local energy storage in **Si capacitors** and voltage regulation with **Low-Dropout Regulators (LDO)**
- **FPGA-controlled current source** provides small continuous current
- Low-mass **Al-Kapton** cables
- **Prototypes** for analog + digital powering of CLICpix ladder

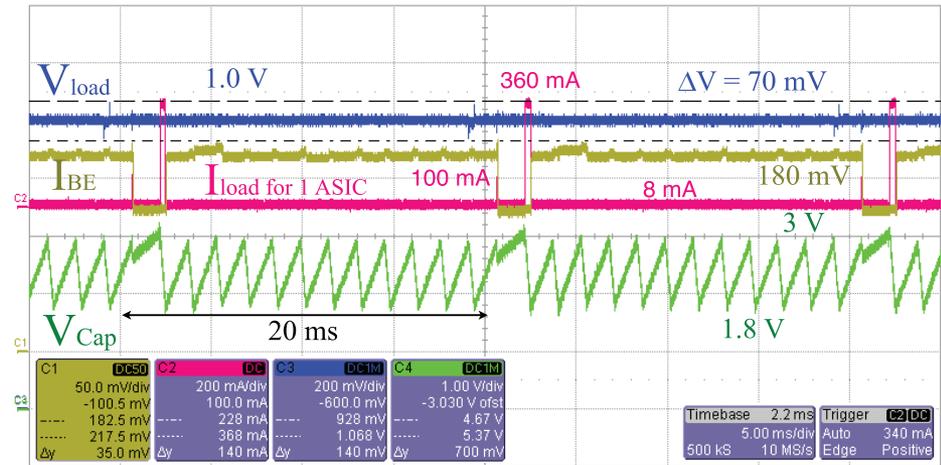
CLICpix power-pulsing + delivery results



analog power

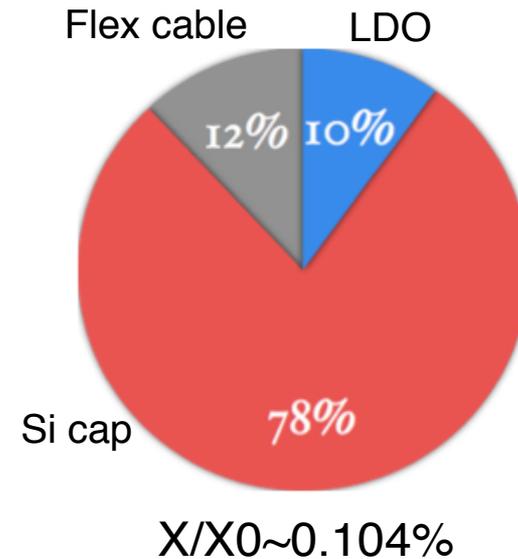


digital power



- Measurements on prototypes for digital and analog powering of ladders:
 - $I_{ladder} < 300\text{ mA}$; $P < 45\text{ mW/cm}^2$
 - Voltage stability:
 - $\Delta V \sim 16\text{ mV}$ (analog), $\sim 70\text{ mV}$ (digital)
 - $\sim 0.1\%$ X_0 material contribution, dominated by Si capacitors
 - Can be reduced to $\sim 0.04\%$ X_0 with evolving Si capacitor technology: $25\ \mu\text{F/cm}^2 \rightarrow 100\ \mu\text{F/cm}^2$

material budget



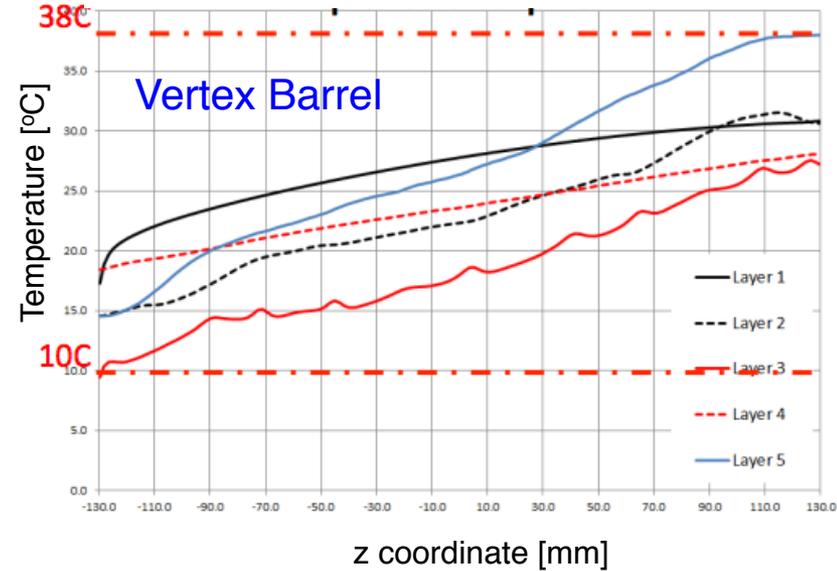
C. Fuentes

Cooling: simulations

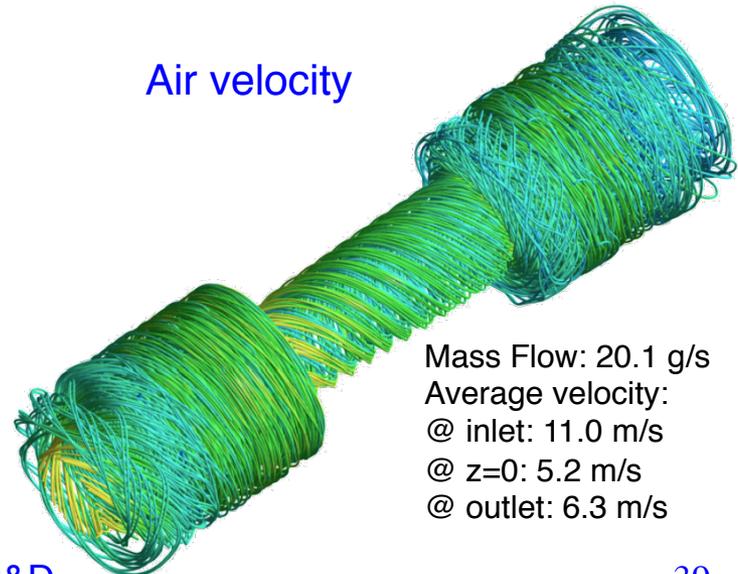
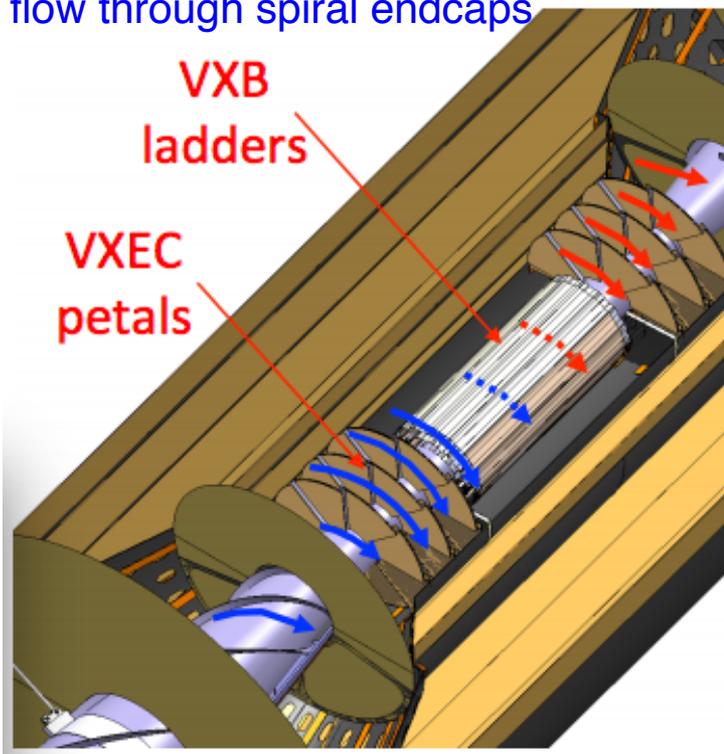
Cooling studies for CLIC vertex detector

- ~ 500 W power dissipation in CLIC vertex area
 - spiral disks allow air flow through detector
 - ANSYS Computational Fluid Dynamic (CFD) finite element simulation
- air cooling seems feasible
- 5-10 m/s flow velocity, 20 g/s mass flow

Temperature profile (FE simulations)



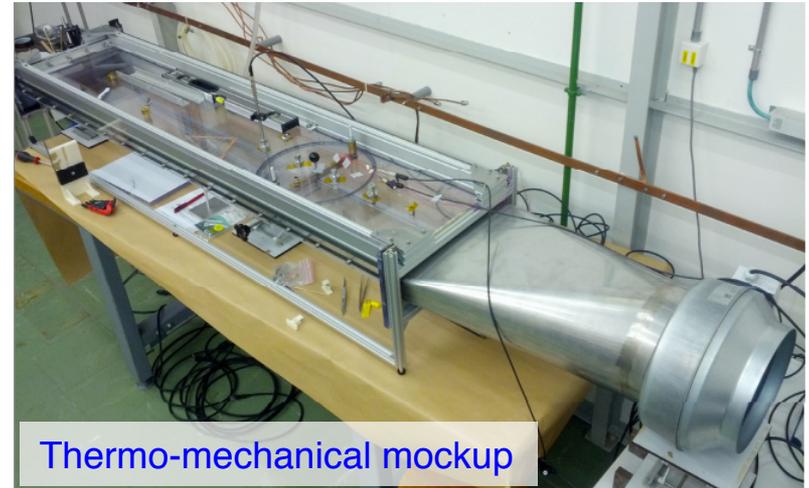
Air flow through spiral endcaps



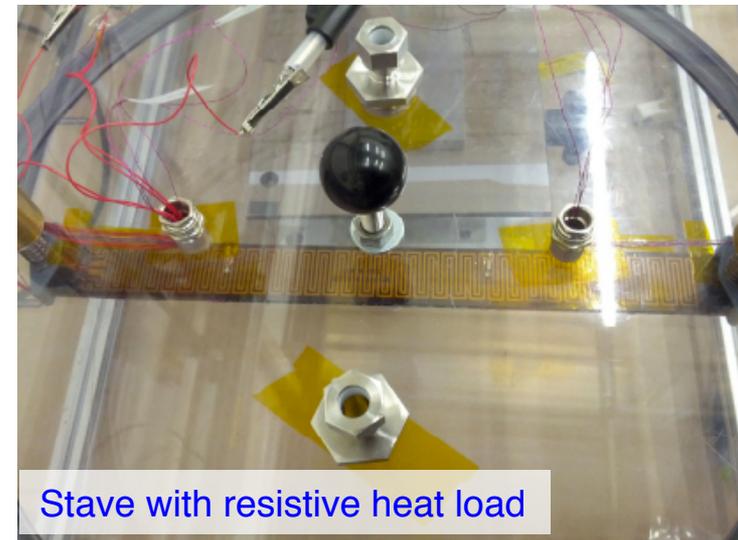
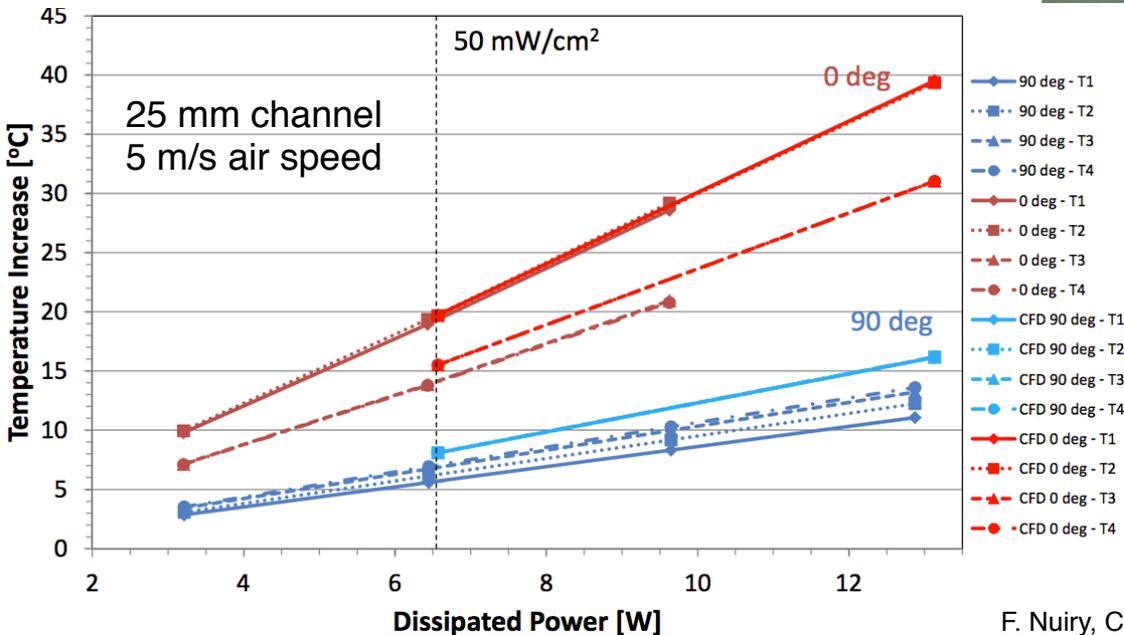
F. Duarte Ramos

Cooling: experimental verification

- built **mock-up** to verify simulations (temperature, vibrations)
- measurements on single stave equipped with resistive heat loads:
 - air flow
 - temperature
 - vibrations (laser sensor)
- comparison with simulation



Temperature increase: measurement + CFD simulation

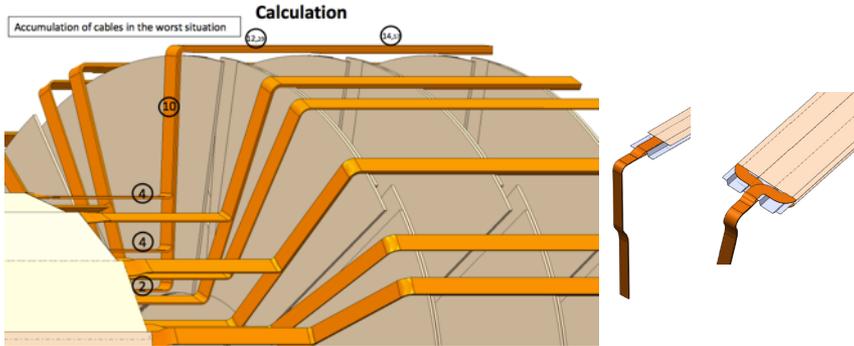


F. Nuiry, C. Bault, F. Duarte Ramos, M.-A. Villarejo Bermudez, W. Klempt

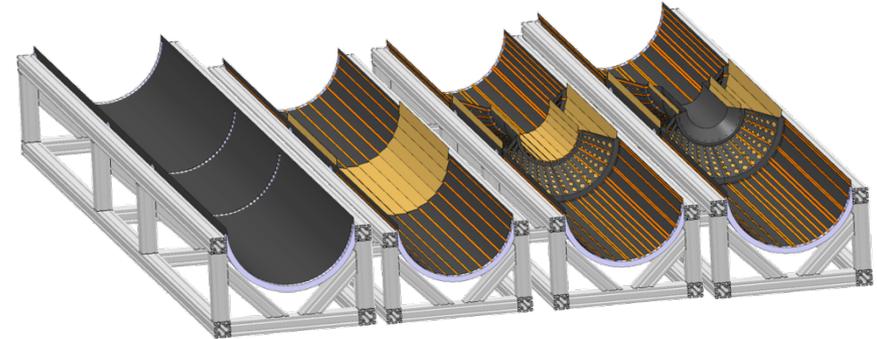
Mechanical integration

- Detector integration: low-mass supports, services, assembly
- Taking into account constraints from powering and cooling
- Detailed material-budget calculations, comparison with simulation models

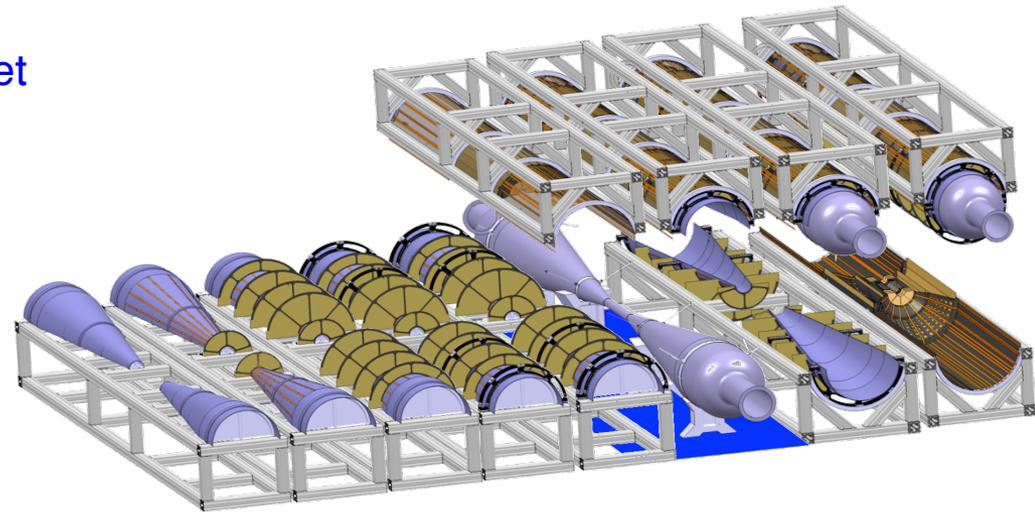
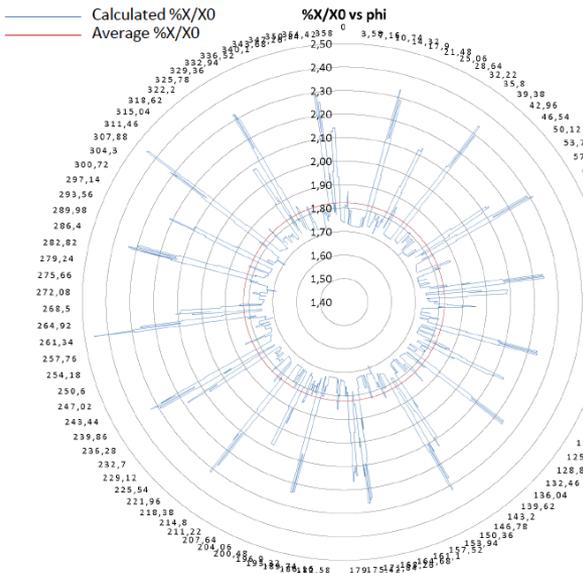
vertex-detector services



assembly scenario



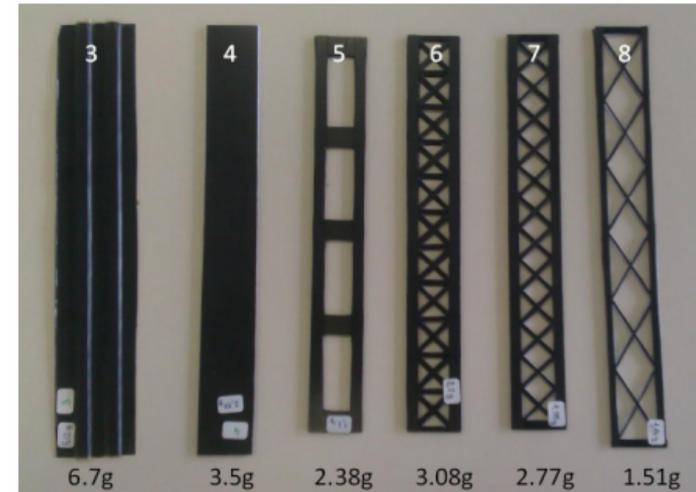
material-budget calculation



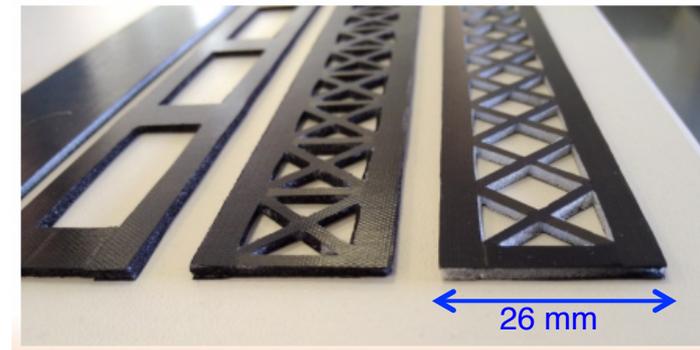
Low-mass supports

- Aim for only $\sim 0.1\%$ X0 per layer for powering + supports
- $\sim 0.05\%$ X0 for supports
- Evaluating various designs and materials based on:
 - Carbon-Fiber-Reinforced Polymers (CFRP)
 - Silicon-Carbide (SiC) foams
- Bending stiffness validated with calculations, finite-element simulations and measurements

CFRP support prototypes



X/X0					
0,156 %	0,134 %	0,091 %	0,118 %	0,106 %	0,058 %

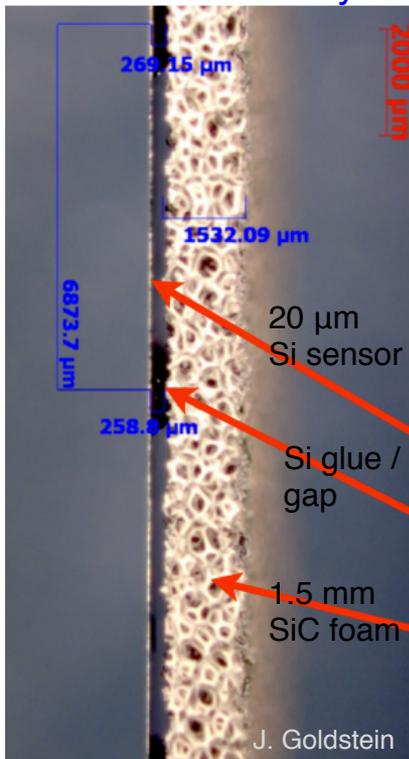


ANSYS FE simulation for CFRP



3-point bending test

SiC foam assembly



J. Goldstein

January 22, 2013

CLIC Vertex R&D

F. Nuiry, C. Bault, F. Duarte Ramos, W. Klempt

Summary and Conclusions

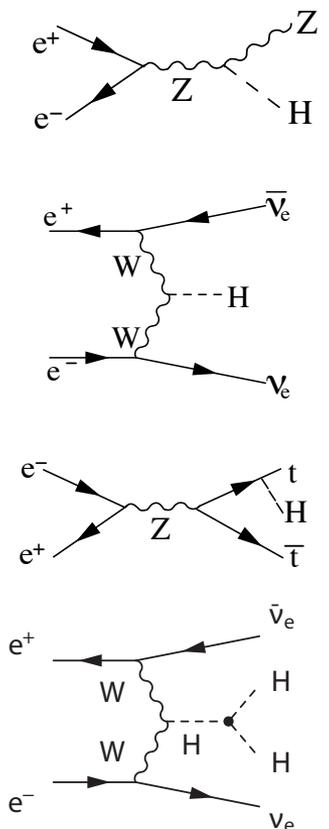
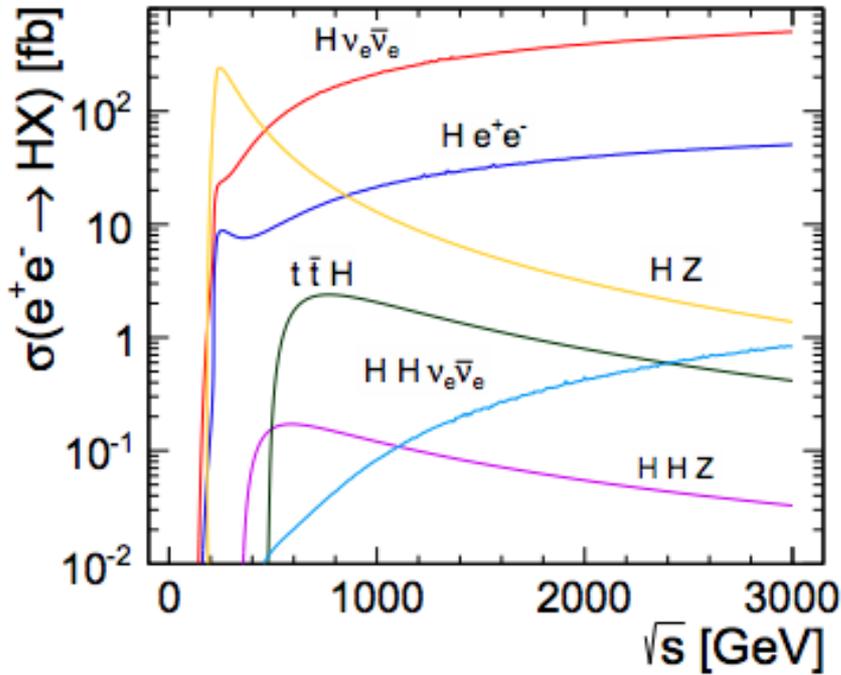


- CLIC accelerator provides:
 - **unique potential** for discovery and precision physics at the TeV scale
 - **challenging requirements** for vertex detectors
- Examples for **active R&D** on the CLIC vertex detector:
 - Hybrid pixel detector technology
 - Power-delivery and power pulsing
 - Detector cooling and mechanical integration
- **Synergy** between CLIC and other vertex-detector R&D projects
- Other groups most **welcome to join** the CLICdp studies

Additional material



Higgs production



Higgs-Strahlung: $e^+e^- \rightarrow ZH$

- Measure H from Z-recoil mass
- Model-independent meas.: m_H, σ
- Measure near threshold: $\sqrt{s} \lesssim 350$ GeV

WW fusion: $e^+e^- \rightarrow H\nu_e\bar{\nu}_e$

- Precise cross-section measurements in $\tau\tau, \mu\mu, qq$ decay modes
- Profits from higher \sqrt{s} (≥ 500 GeV)

Radiation off top-quarks: $e^+e^- \rightarrow t\bar{t}H$

- Measure top Yukawa coupling
- Needs $\sqrt{s} \geq 500$ GeV

Double-Higgs prod.: $e^+e^- \rightarrow HH\nu_e\bar{\nu}_e$

- Measure tri-linear self coupling
- Needs high \sqrt{s} (≥ 1.5 TeV)

Complementary Higgs measurements by accessing wide energy range:

$m_H=125$ GeV	250 GeV	350 GeV	500 GeV	1 TeV	1.5 TeV	3 TeV
$\sigma(e^+e^- \rightarrow ZH)$	240 fb	129 fb	57 fb	13 fb	6 fb	1 fb
$\sigma(e^+e^- \rightarrow H\nu_e\bar{\nu}_e)$	8 fb	30 fb	75 fb	210 fb	309 fb	484 fb
Int. \mathcal{L} (4-5 years)	250 fb^{-1}	350 fb^{-1}	500 fb^{-1}	1000 fb^{-1}	1500 fb^{-1}	2000 fb^{-1}
# ZH events	60000	45500	28500	13000	7500	2000
# $H\nu_e\bar{\nu}_e$	2000	10500	37500	210000	460000	970000

CLIC two-beam acceleration scheme



Two-beam acceleration scheme

- No individual RF power sources
- Demonstrated in dedicated test facility at CERN (CTF3)

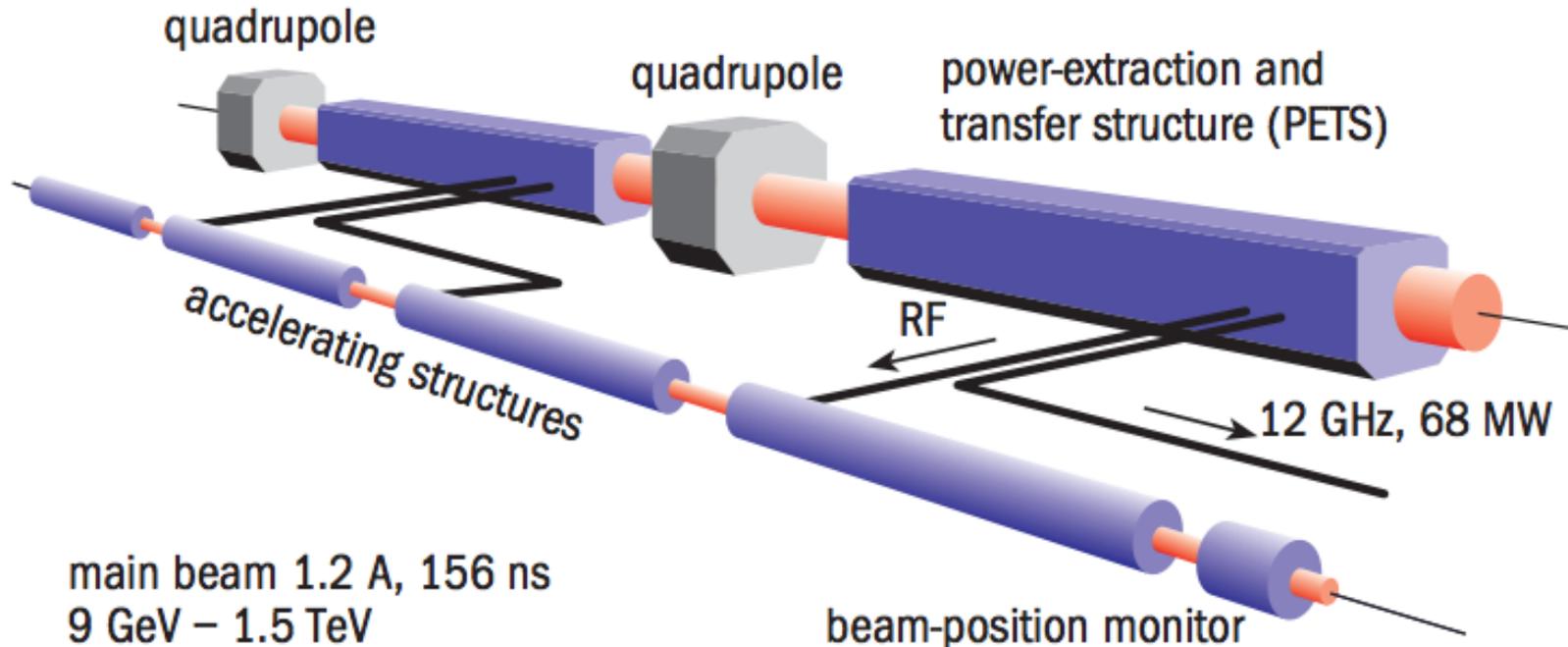
Drive Beam supplies RF power

- 12 GHz bunch structure
- low energy e^- (2.4 GeV - 240 MeV)
- high current (100A)

Main beam for physics

- high energy e^+/e^- (9 GeV – 1.5 TeV)
- low current 1.2 A

drive beam 100 A, 239 ns
2.38 GeV – 240 MeV



main beam 1.2 A, 156 ns
9 GeV – 1.5 TeV

January 22, 2013

CLIC Vertex R&D

LC pixel R&D examples



Project	Technology	Target experiments	Groups
Mimosa	fully integrated CMOS MAPS Tower Jazz 0.18 um	ALICE, CBM, BES-3, ILD@ILC	IPHC Strasbourg
Arachnid / Cherwell		generic vtx / tracking / calo, ALICE ITS	Bristol, Birmingham, Queen Mary, RAL, Daresbury
Chronopix	fully integrated CMOS MAPS IBM 90 nm	SiD@ILC	Oregon
FPCCD	integrated sensor , separate r/o, Hamamatsu CCDs	ILD@ILC	KEK, Tohoku
DEPFET	integrated sensor , separate readout, MPG-HLL DEPFET	Belle II, ILD@ILC	Bonn, MPI Munich, Barcelona, Santander, others
VIP2b / SDR / MAMBO4	3d integrated / SOI Tezzaron + STM 130 nm, MIT LL	generic technology tests, Super-Belle, SiD@ILC	FNAL, KEK, OKI, INFN, others
HV-CMOS CCPD	active sensor , 180 nm CMOS	HL-ATLAS, CLIC	Heidelberg, CERN, CPPM, Bonn, Geneva
CLICpix	hybrid r/o , 65 nm CMOS	CLIC, SiD@ILC	CERN

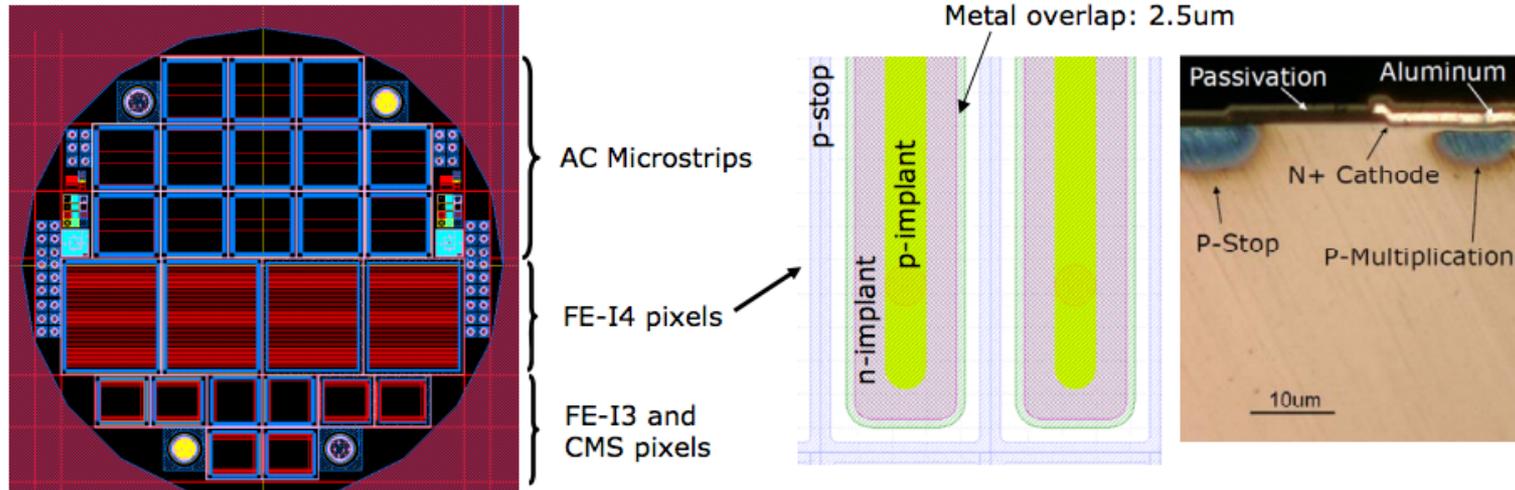
Low Gain Avalanche Detectors (LGAD)

RD50 project:

Fabrication of new p-type pixel detectors with enhanced multiplication effect in the n-type electrodes

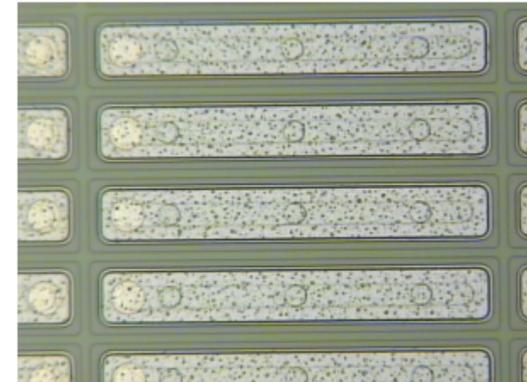
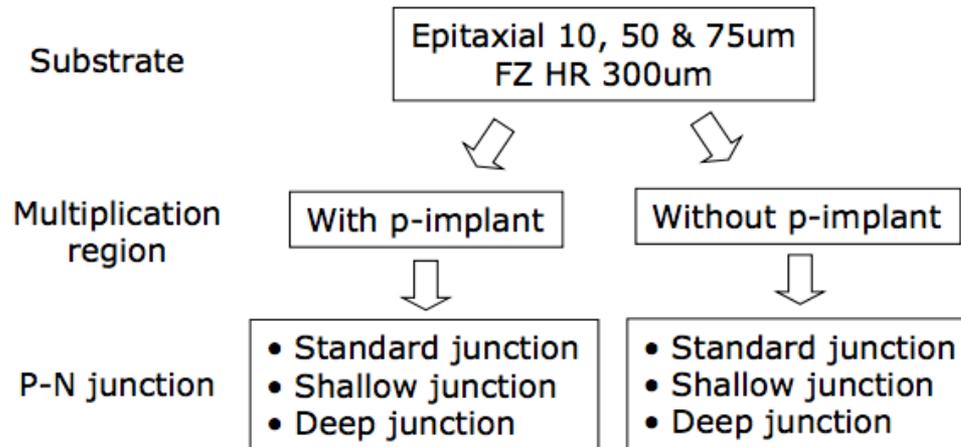
Institutes participating in this project:

G. Pellegrini (IMB-CNM), G. Casse (Liverpool University), H. Sadrozinski (UCSC), S. Grinstein (IFAE), W. de Boer (KIT), I. Vila (IFCA), R. Bates (University Glasgow), M. Bruzzi (INFN Florence) M. Moll (CERN)

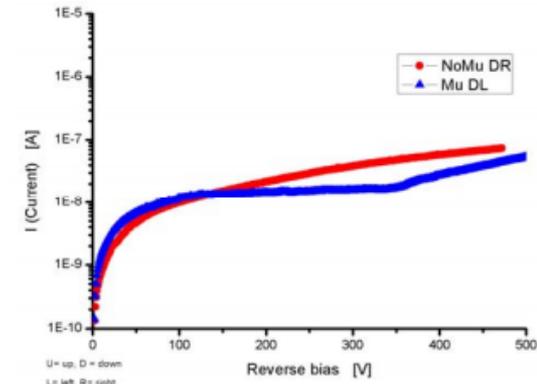


See G. Pellegrini's talk at CLIC January meeting, S. Hidalgo's talk at RD50 meeting at Albuquerque (2013) and H. Sadrozinski, "Exploring charge multiplication for fast timing with silicon sensors" 20th RD50 Workshop, Bari (2012)

Low Gain Avalanche Detectors (LGAD): run



FE-I4 pixel sensor



AC Microstrip Epi 50um deep junction

Run finished this summer.
Sensors currently characterized at UC Santa Cruz by M. Baselga (Ph.D. student – IMB-CNM)

See G. Pellegrini's talk at CLIC January meeting and H. Sadrozinski, "Exploring charge multiplication for fast timing with silicon sensors" 20th RD50 Workshop, Bari (2012)

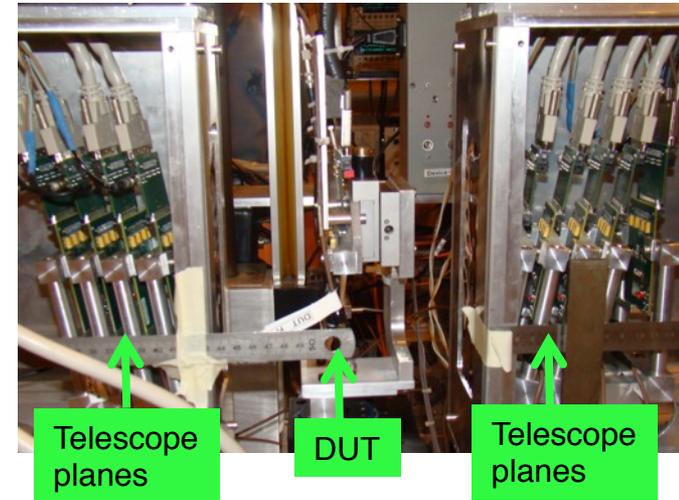
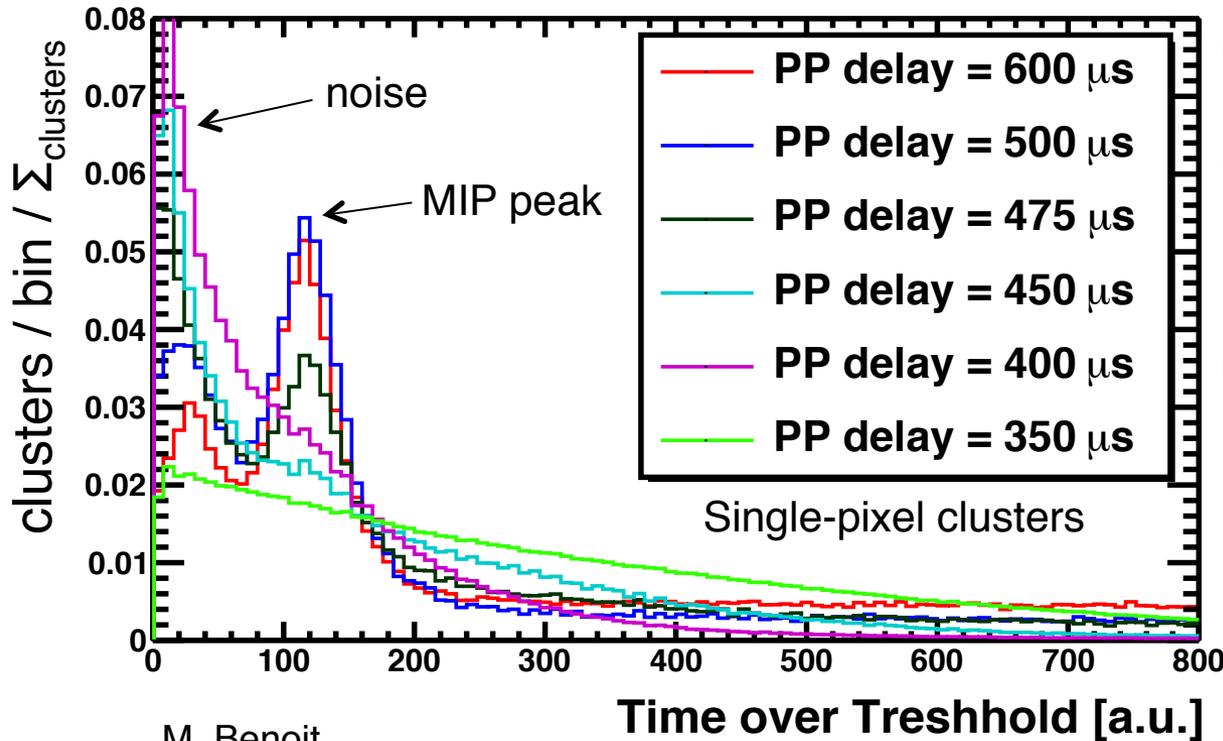
Power-pulsing in test beam

Power Pulsing with Timepix:

- Not designed for power pulsing, single bias line for all pixel rows
- But possibility to switch on/off all preamps through bias DAC

CERN SPS test-beam campaign in June 2012:

- Power pulsing of the Chip and operation in sync with LHCb/Timepix tracking telescope
- Shutter-based readout for 25 μs
- Adjustable delay between power-on and shutter-start times



- Fully efficient after $\sim 600 \mu\text{s}$
- Similar results obtained with [source](#) in laboratory and in [simulation](#)